

Title: New Directions in Dark Matter Direct Detection

Date: Apr 04, 2017 01:00 PM

URL: <http://pirsa.org/17040029>

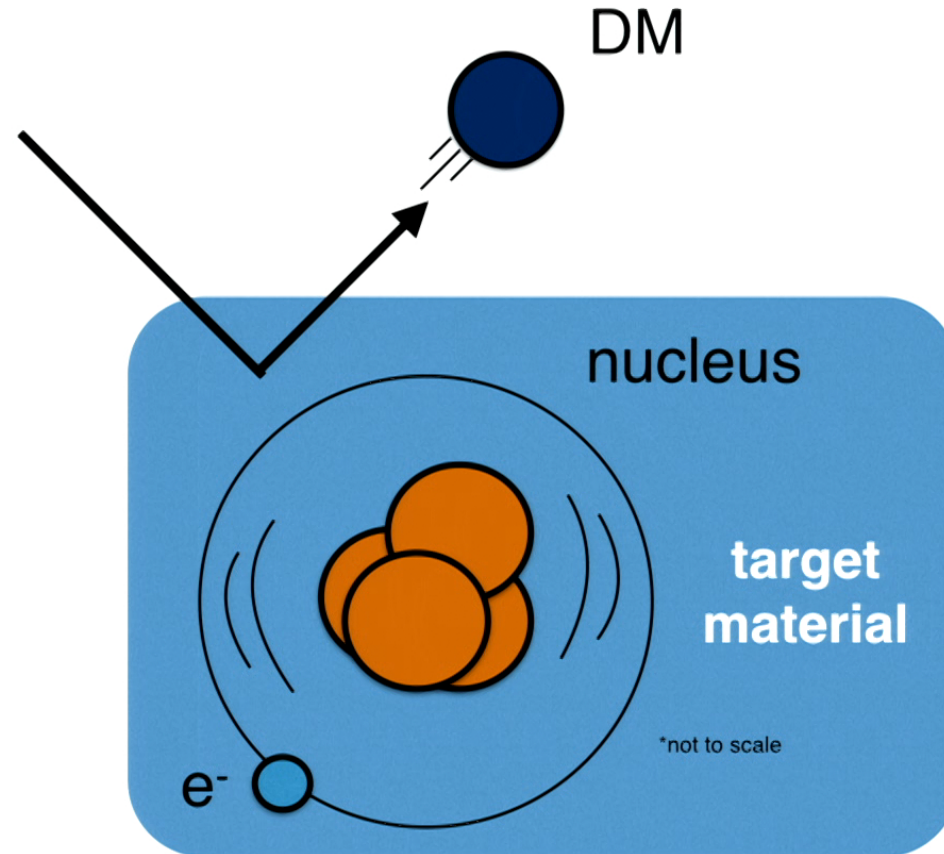
Abstract: <p>Sub-GeV dark matter is a theoretically motivated but largely unexplored paradigm of dark matter. In this talk, I will discuss recent work on the direct detection of sub-GeV dark matter through dark matter-electron scattering. I will present some motivated models that can be probed with these techniques as well as projections for current and near-term noble liquid, semiconductor, and scintillator experiments. Finally, I will discuss some new techniques that may allow us to more robustly discriminate between dark matter signatures and background.</p>

New Directions for DM Direct Detection

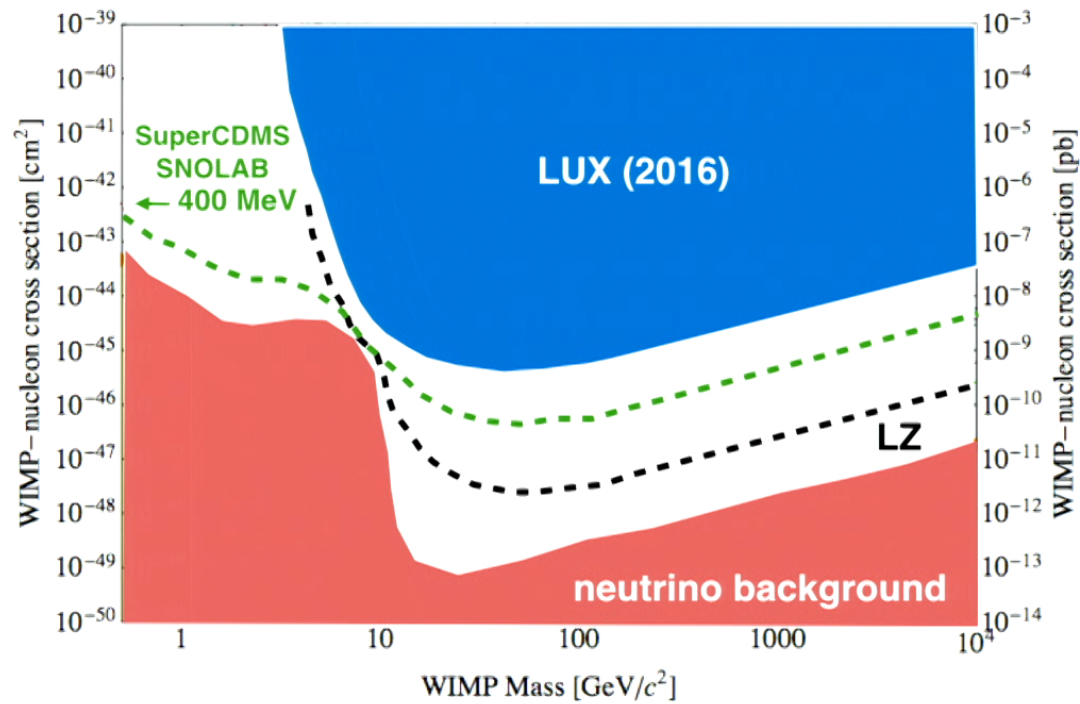
Tien-Tien Yu (CERN)

Perimeter Institute — April 4, 2017

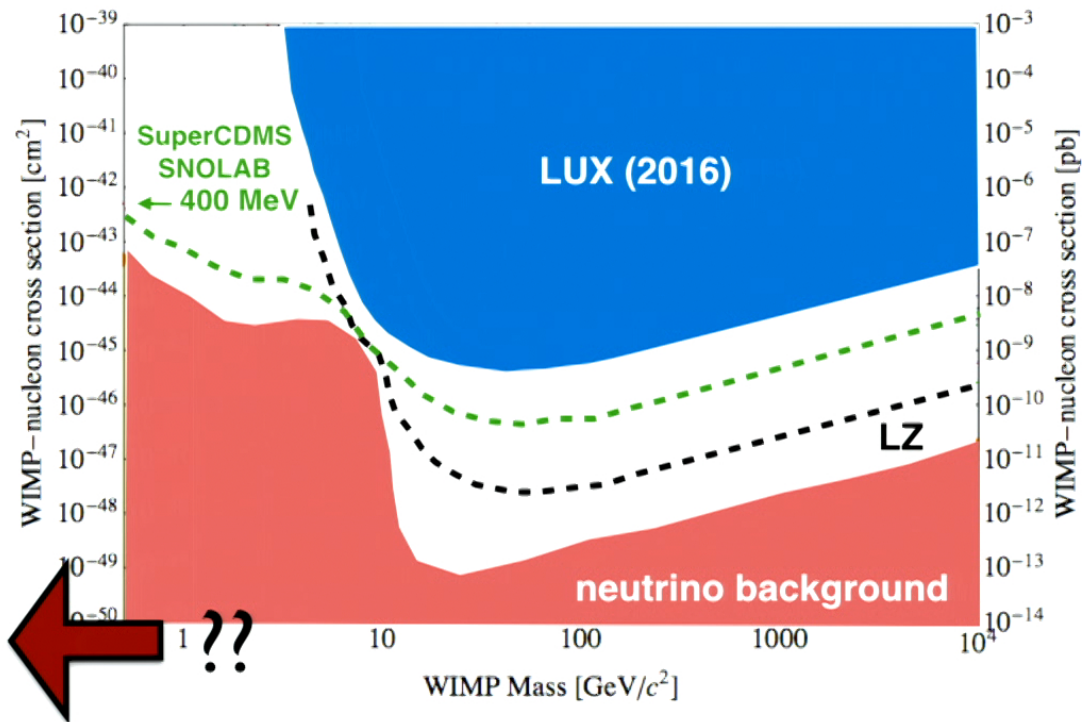
DM direct detection

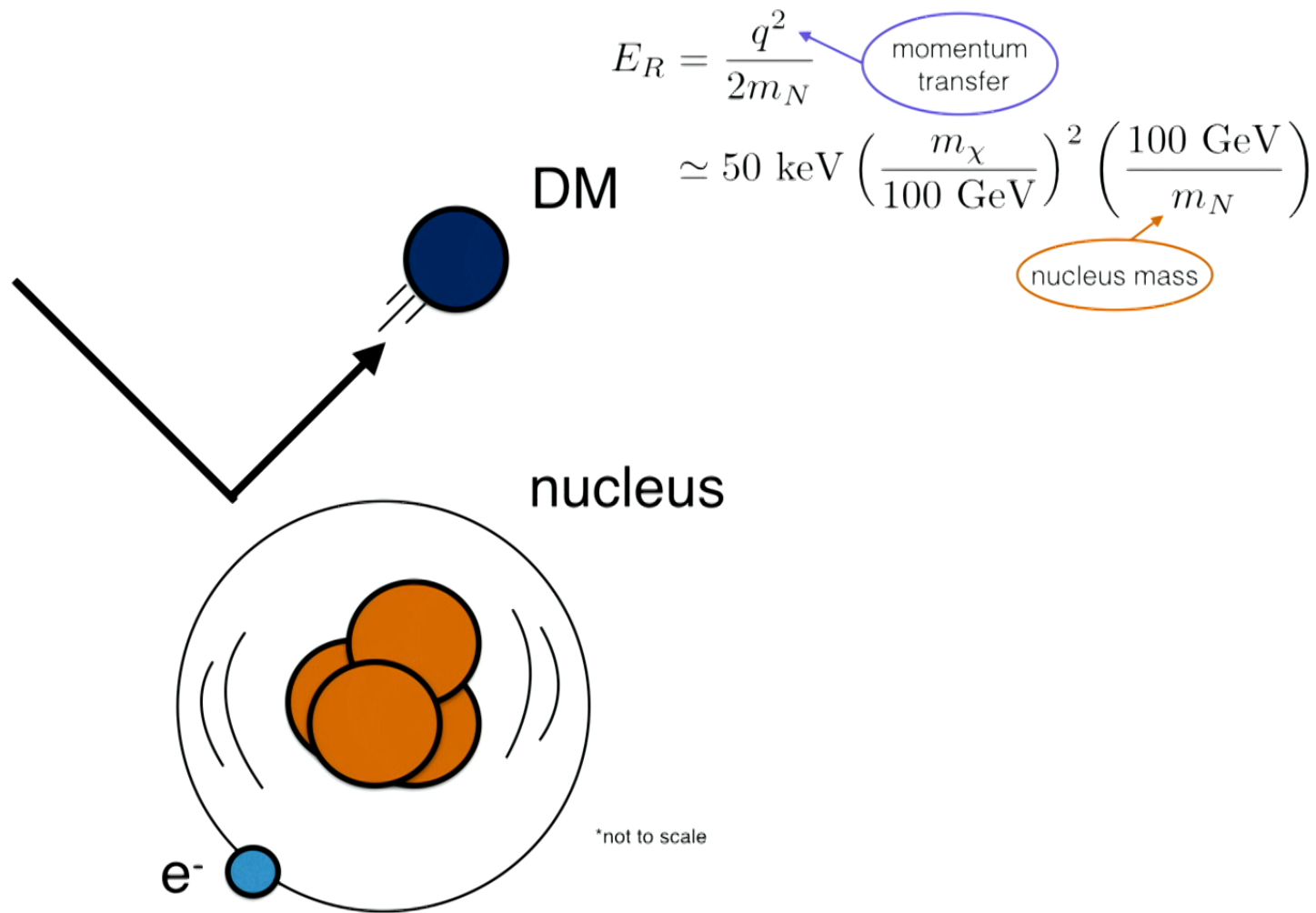


DM direct detection

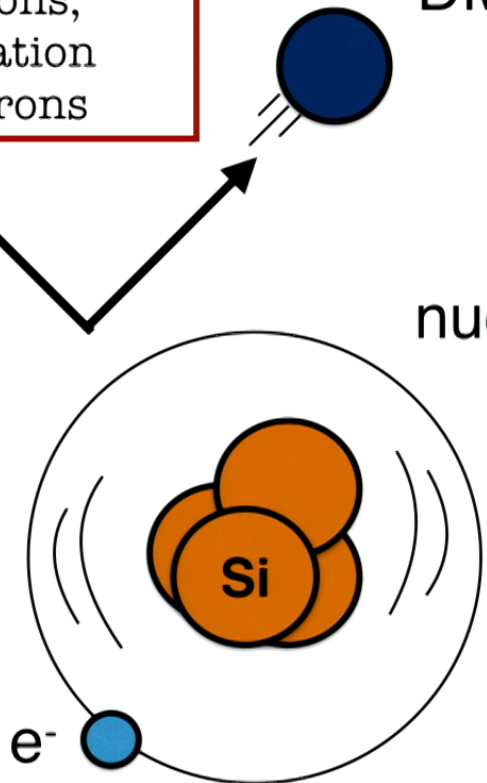


DM direct detection





signal:
 phonons,
 scintillation
 photons,
 ionization
 electrons



DM

nucleus

*not to scale

$$E_R = \frac{q^2}{2m_N}$$

momentum transfer

$$\simeq 50 \text{ keV} \left(\frac{m_\chi}{100 \text{ GeV}} \right)^2 \left(\frac{100 \text{ GeV}}{m_N} \right)$$

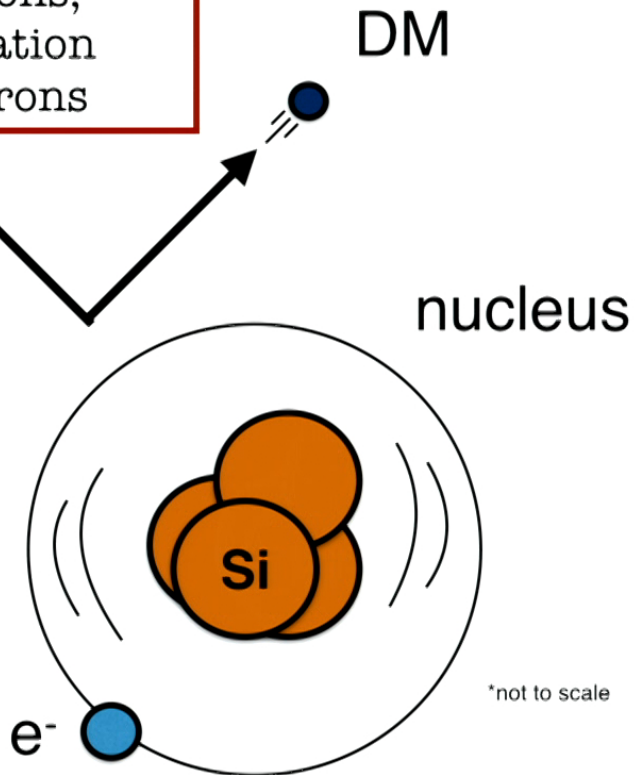
nucleus mass

$$m_N = 28 \text{ GeV}$$

$$m_\chi = 100 \text{ GeV}$$

$$E_R \sim 100 \text{ keV}$$

signal:
phonons,
scintillation
photons,
ionization
electrons



$$E_R = \frac{q^2}{2m_N}$$

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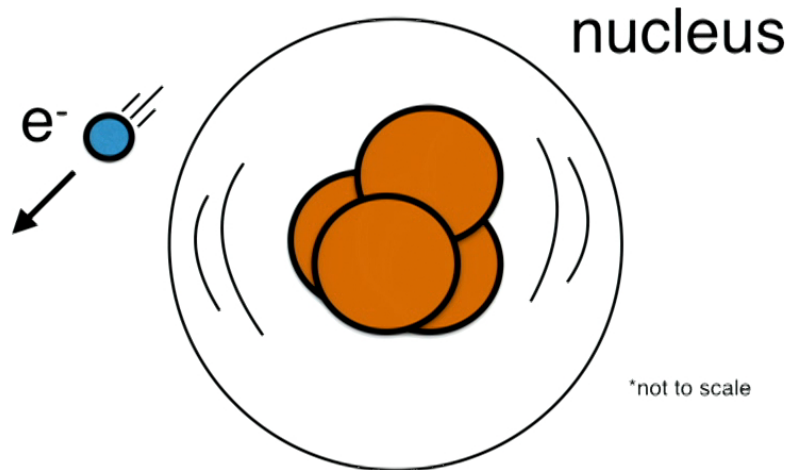
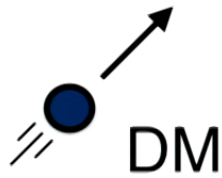
$$m_N = 28 \text{ GeV}$$

$$m_\chi = 100 \text{ MeV}$$

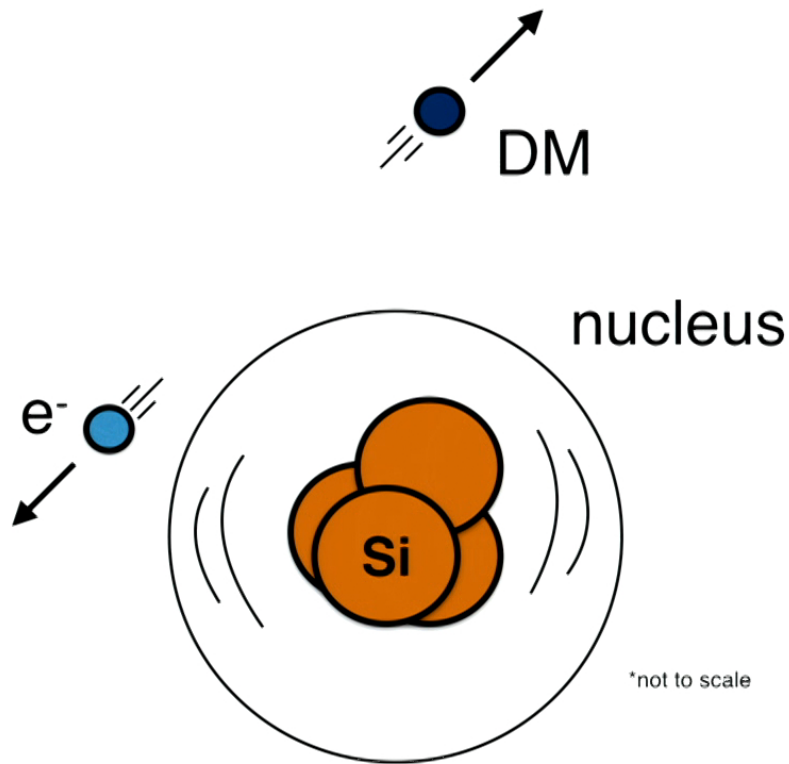
$$E_R \sim 0.1 \text{ eV}$$

signal:
a few ionized
electrons

$$E_R = \vec{q} \cdot \vec{v} - \frac{q^2}{2\mu_{\chi N}}$$
$$\sim \frac{1}{2} \text{eV} \times \left(\frac{m_\chi}{\text{MeV}} \right)$$



signal:
a few ionized
electrons



$$E_R = \vec{q} \cdot \vec{v} - \frac{q^2}{2\mu_{\chi N}}$$
$$\sim \frac{1}{2} \text{eV} \times \left(\frac{m_\chi}{\text{MeV}} \right)$$

$$m_N = 28 \text{ GeV}$$

$$m_\chi = 100 \text{ MeV}$$

$$E_R \sim 50 \text{ eV}$$

Calculation

ingredients

astrophysics

$$\frac{d\langle\sigma v\rangle}{d\ln E_R} = \frac{\bar{\sigma}_e}{8\mu_{\chi e}^2} \int q dq |f(k, q)|^2 |F_{DM}(q)|^2 \eta(v_{min})$$

$$\eta(v_{min}) = \int_{v_{min}} \frac{d^3v}{v} f_{MB}(\vec{v})$$

$$v_{min} = \frac{E_R + E_B}{q} + \frac{q}{2m_\chi}$$

ingredients

particle physics

$$\frac{d\langle\sigma v\rangle}{d\ln E_R} = \frac{\bar{\sigma}_e}{8\mu_{\chi e}^2} \int q dq |f(k, q)|^2 |F_{DM}(q)|^2 \eta(v_{min})$$

$$\bar{\sigma}_e = \frac{\mu_{\chi e}^2}{16\pi m_\chi^2 m_e^2} \overline{|\mathcal{M}_{\chi e}(q)|^2}_{q^2=\alpha^2 m_e^2}$$

$$\sigma(q) = \bar{\sigma}_e \times |F_{DM}(q)|^2$$

ingredients

material dependent

$$\frac{d\langle\sigma v\rangle}{d\ln E_R} = \frac{\bar{\sigma}_e}{8\mu_{\chi e}^2} \int q dq |f(k, q)|^2 |F_{DM}(q)|^2 \eta(v_{min})$$

$$|f(k, q)|^2 = \left| \int d^3x \psi_f^*(\vec{x}) \psi_i(\vec{x}) e^{i\vec{q}\cdot\vec{x}} \right|^2$$

wave-function overlap between initial
and final electron states

probability of going from state i to i'

ingredients

$$\frac{d\langle\sigma v\rangle}{d\ln E_R} = \frac{\bar{\sigma}_e}{8\mu_{\chi e}^2} \int q dq |f(k, q)|^2 |F_{DM}(q)|^2 \eta(v_{min})$$

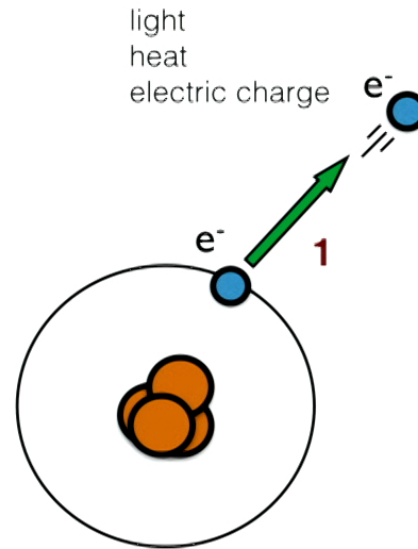
local DM density

$$R = N_T \frac{\rho_\chi}{m_\chi} \int_{E_{R,cut}} d\ln E_R \frac{d\langle\sigma v\rangle}{d\ln E_R}$$

number of target nuclei per unit mass

energy threshold

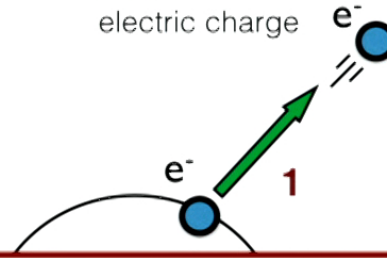
noble liquid



$$|f_{ion}^{nl}(k', q)|^2 = \frac{4k'^3}{(2\pi)^3} \sum_{l'l} (2l+1)(2l'+1)(2L+1) \times \begin{bmatrix} l & l' & L \\ 0 & 0 & 0 \end{bmatrix}^2 \left| \int r^2 dr R_{k'l'}(r) R_{nl}(r) j_L(qr) \right|^2$$

noble liquid

light
heat
electric charge

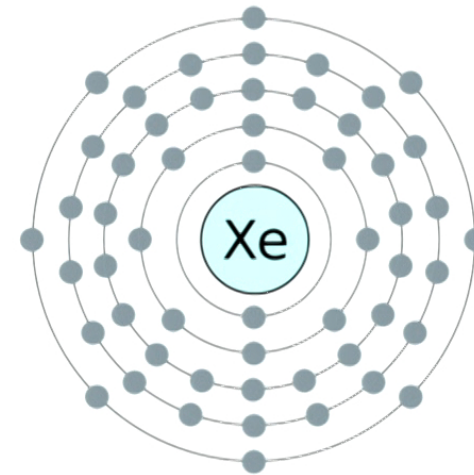
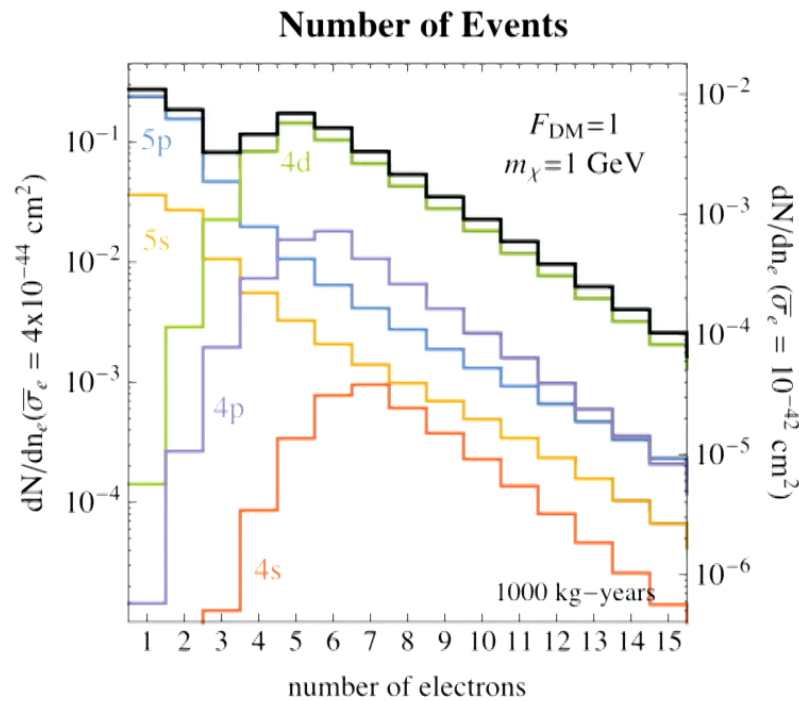


electron wave functions
calculated
with Hartree-Fock method
for atoms

$$|f_{ion}^{nl}(k', q)|^2 = \frac{4k'^3}{(2\pi)^3} \sum_{l'l} (2l+1)(2l'+1)(2L+1) \\ \times \begin{bmatrix} l & l' & L \\ 0 & 0 & 0 \end{bmatrix}^2 \left| \int r^2 dr R_{k'l'}(r) R_{nl}(r) j_L(qr) \right|^2$$

XENON

54: Xenon



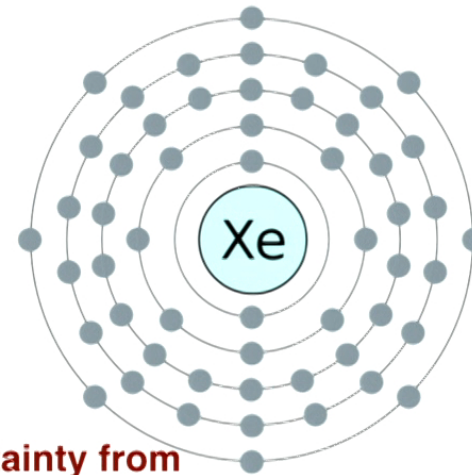
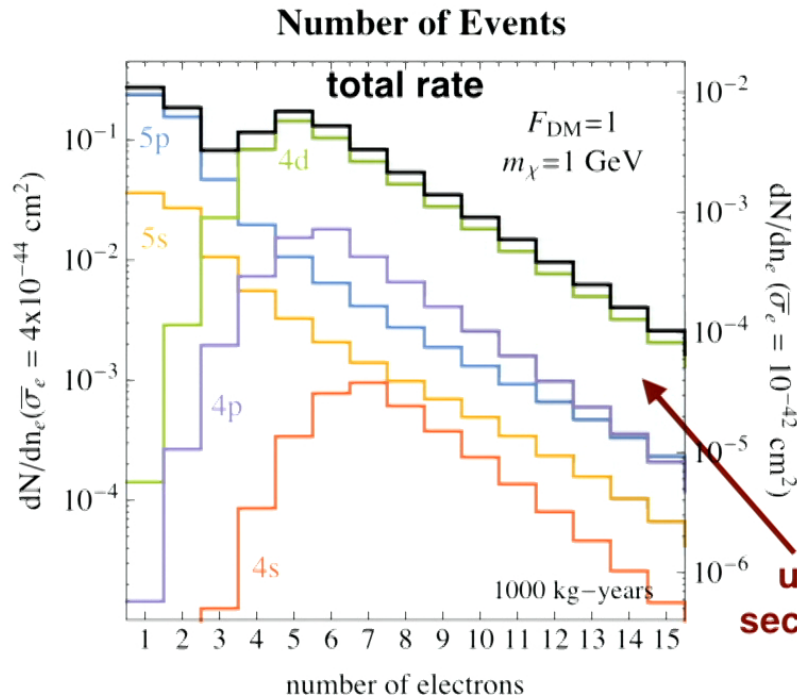
http://commons.wikimedia.org/wiki/Category:Electron_shell_diagrams

Essig, Volansky, TTY [1703.00910]

Electron configuration:
[Ar] 3d¹⁰ 4s² 4p⁶ 4d¹⁰ 5s² 5p⁶

XENON

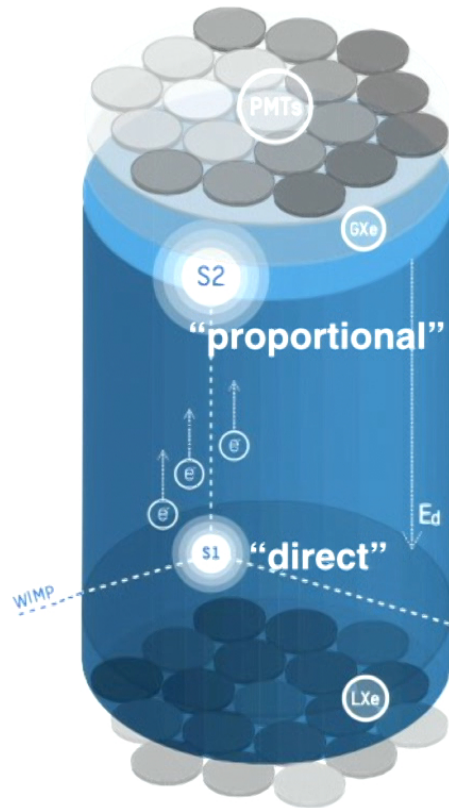
54: Xenon



Electron configuration:
[Ar] 3d¹⁰ 4s² 4p⁶ 4d¹⁰ 5s² 5p⁶

Essig, Volansky, TTY [1703.00910]

a XENON detector



i.e. XENON10, XENON100, XENON1T, LUX

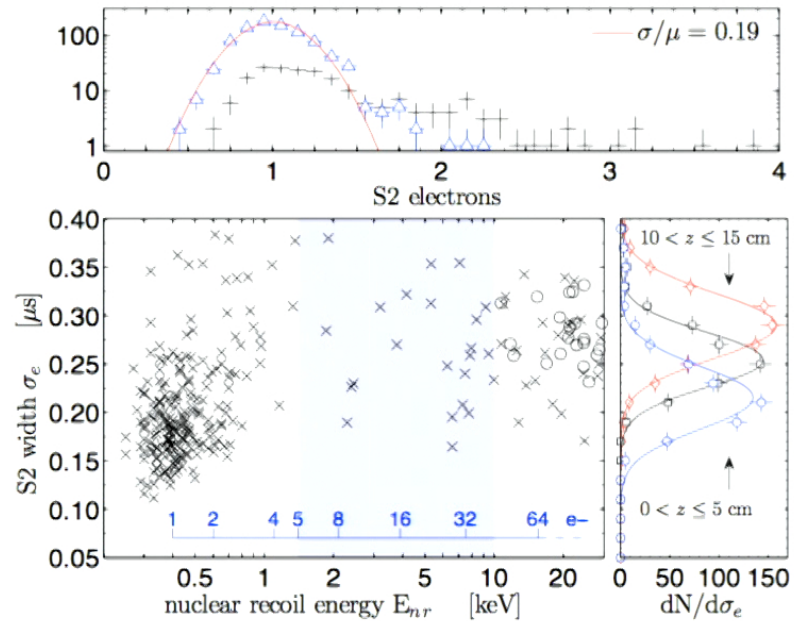
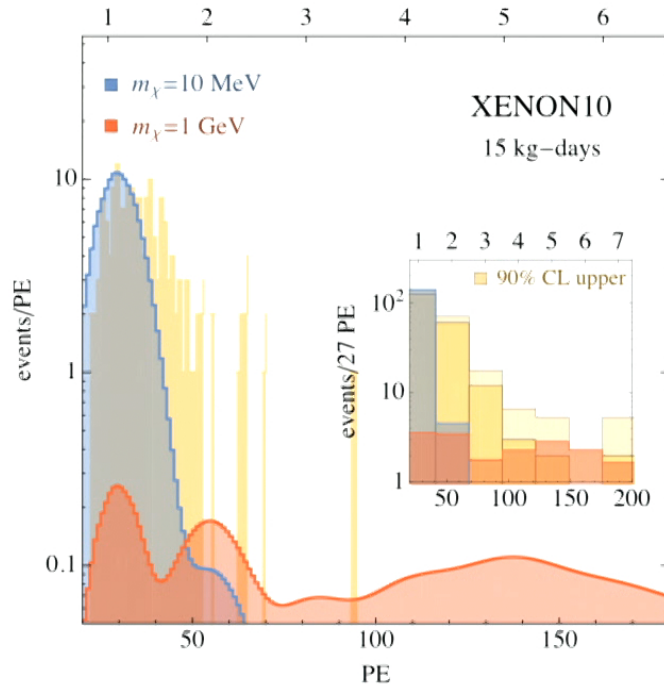
DM-electron scattering
=
S2 only signal

measures **PhotoE**lectrons

https://commons.wikimedia.org/wiki/File:2phaseTPC_b.jpg

XENON10

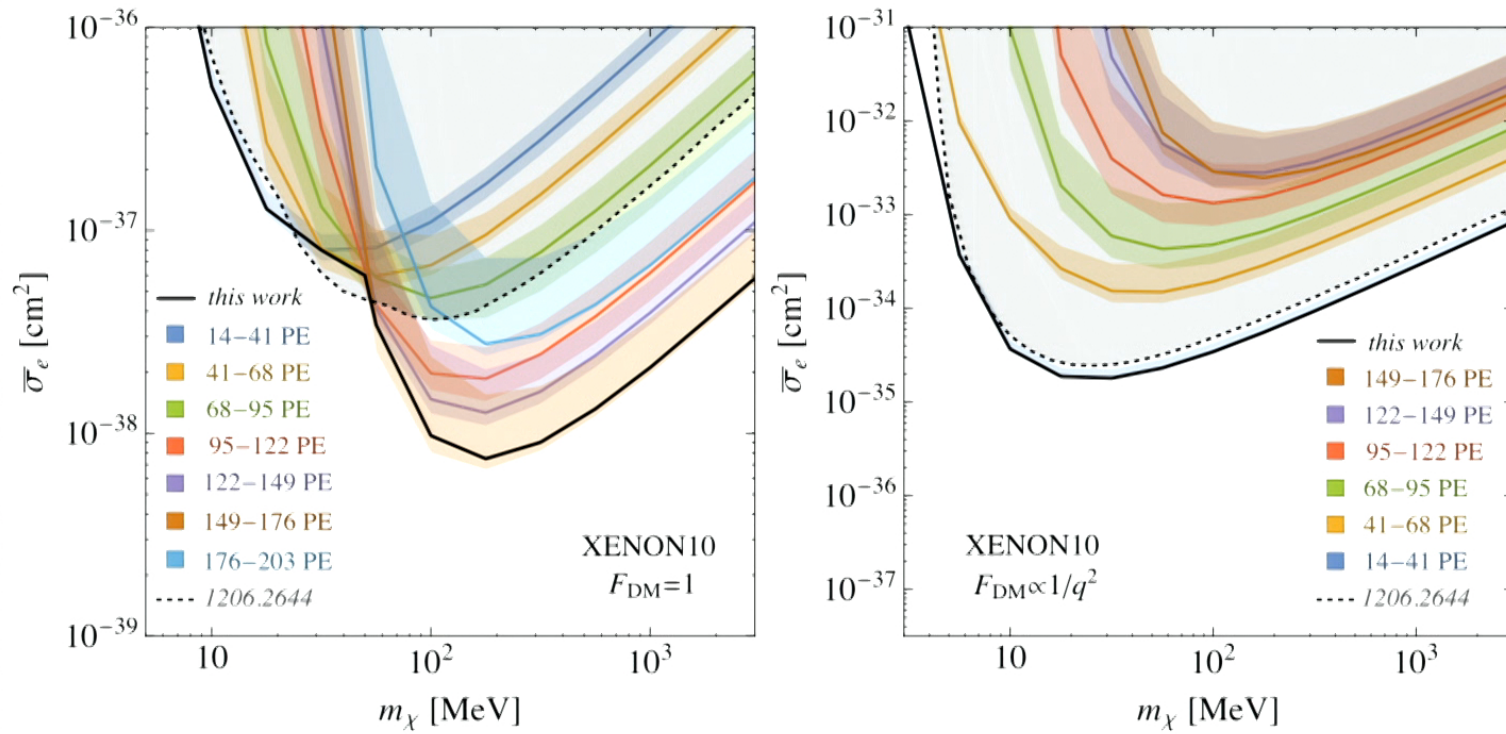
ne~27 PE



Essig, Volansky, TTY [1703.00910]

XENON10 Collaboration
 Phys.Rev.Lett. **110** (2013) 249901

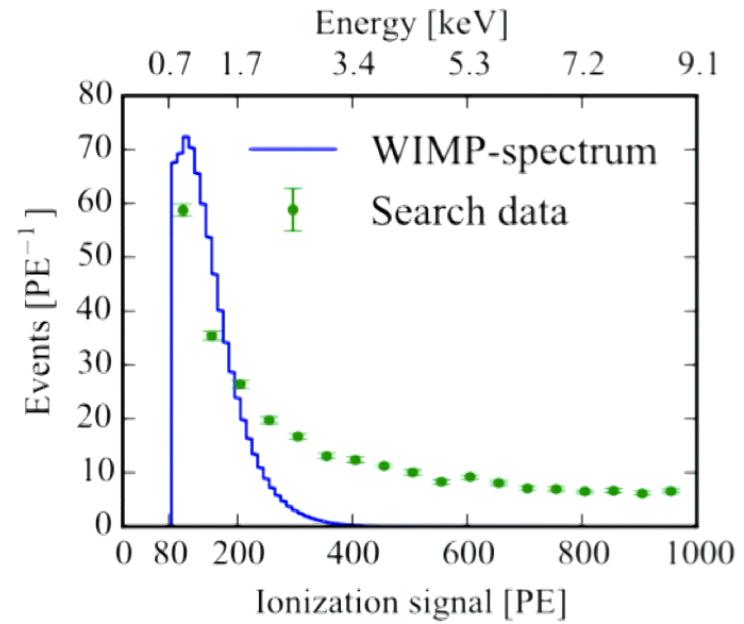
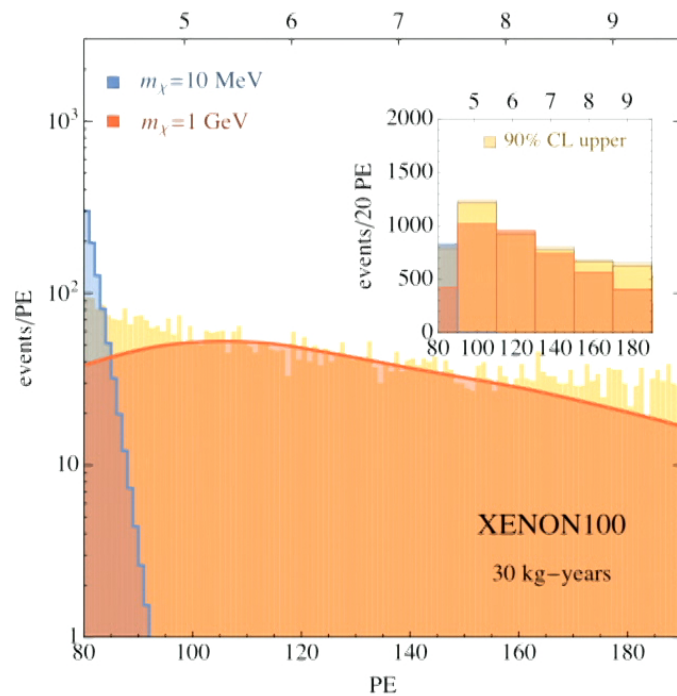
XENON10



Essig, Volansky, TTY [1703.00910]

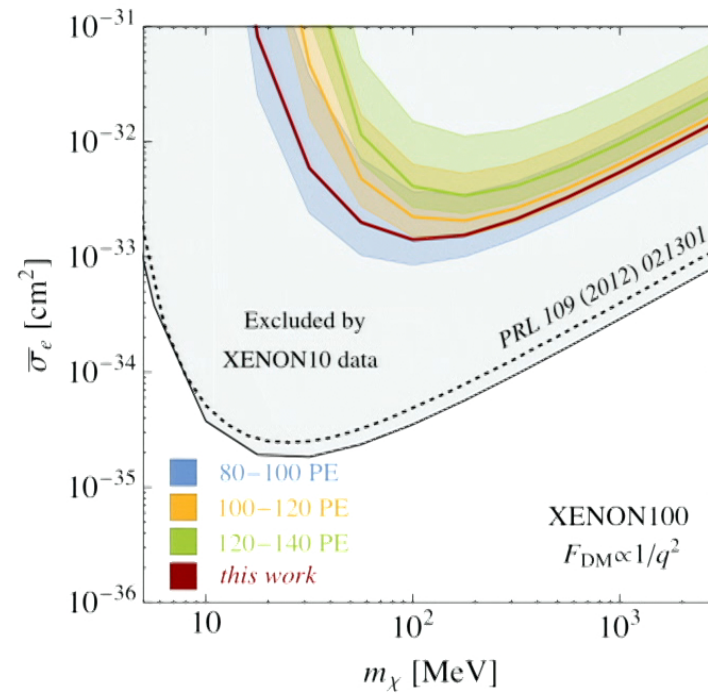
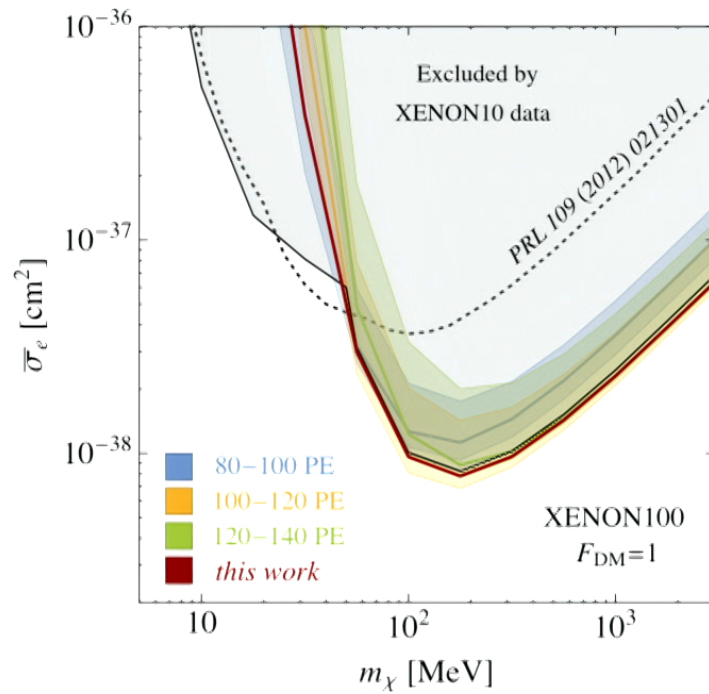
XENON100

ne~20 PE



Essig, Volansky, TTY [1703.00910]

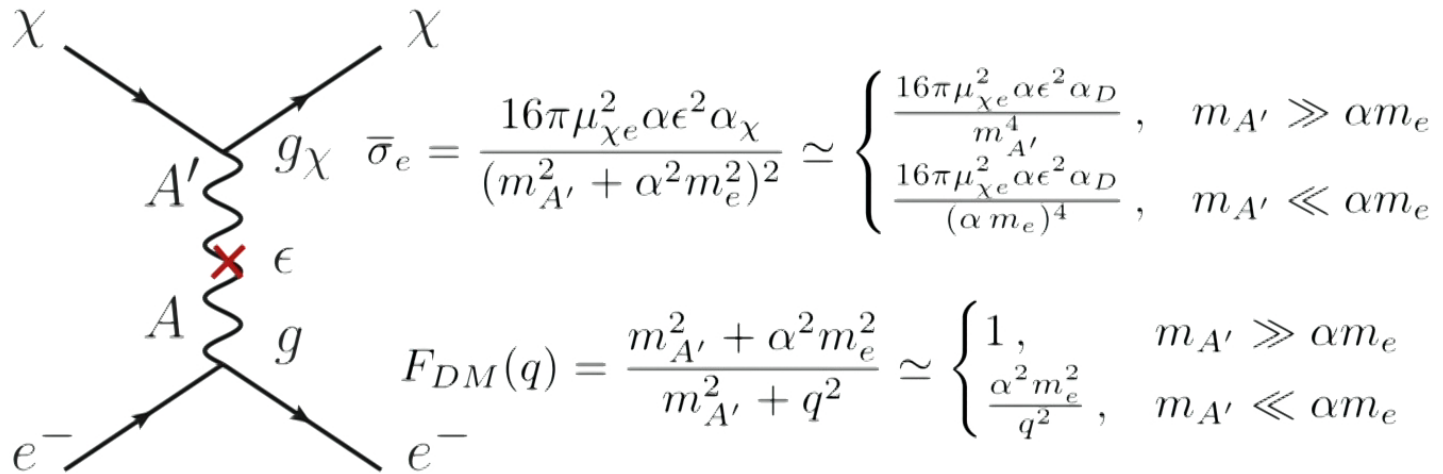
XENON100



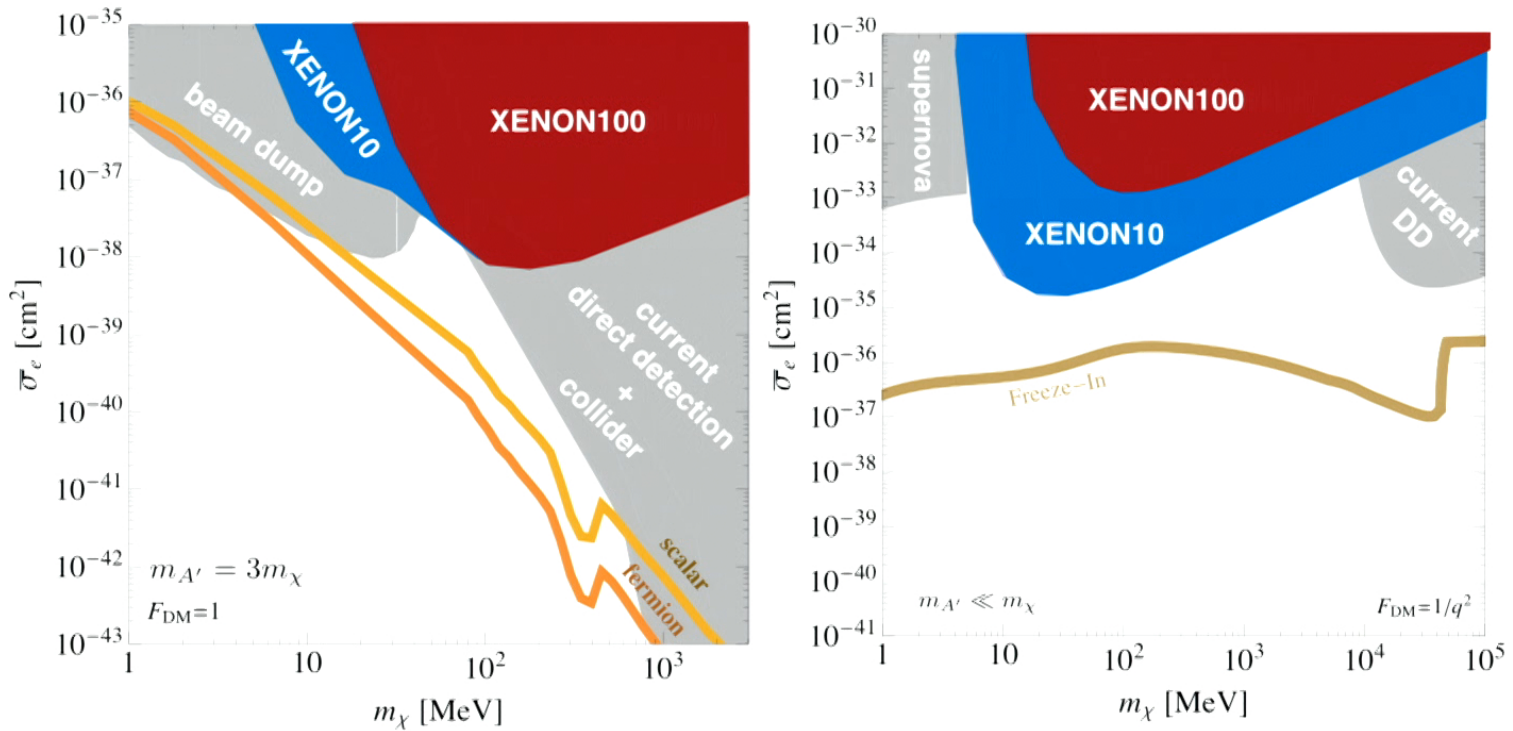
Essig, Volansky, TTY [1703.00910]

A Model: Hidden Photon

$$\mathcal{L} = F_{\mu\nu}^2 + F'^2_{\mu\nu} + m_{A'}^2 A'^2_{\mu} + g_{\chi} J^{\mu}_{\chi} A'_{\mu} + g J^{\mu}_e (A_{\mu} + \epsilon A'_{\mu})$$

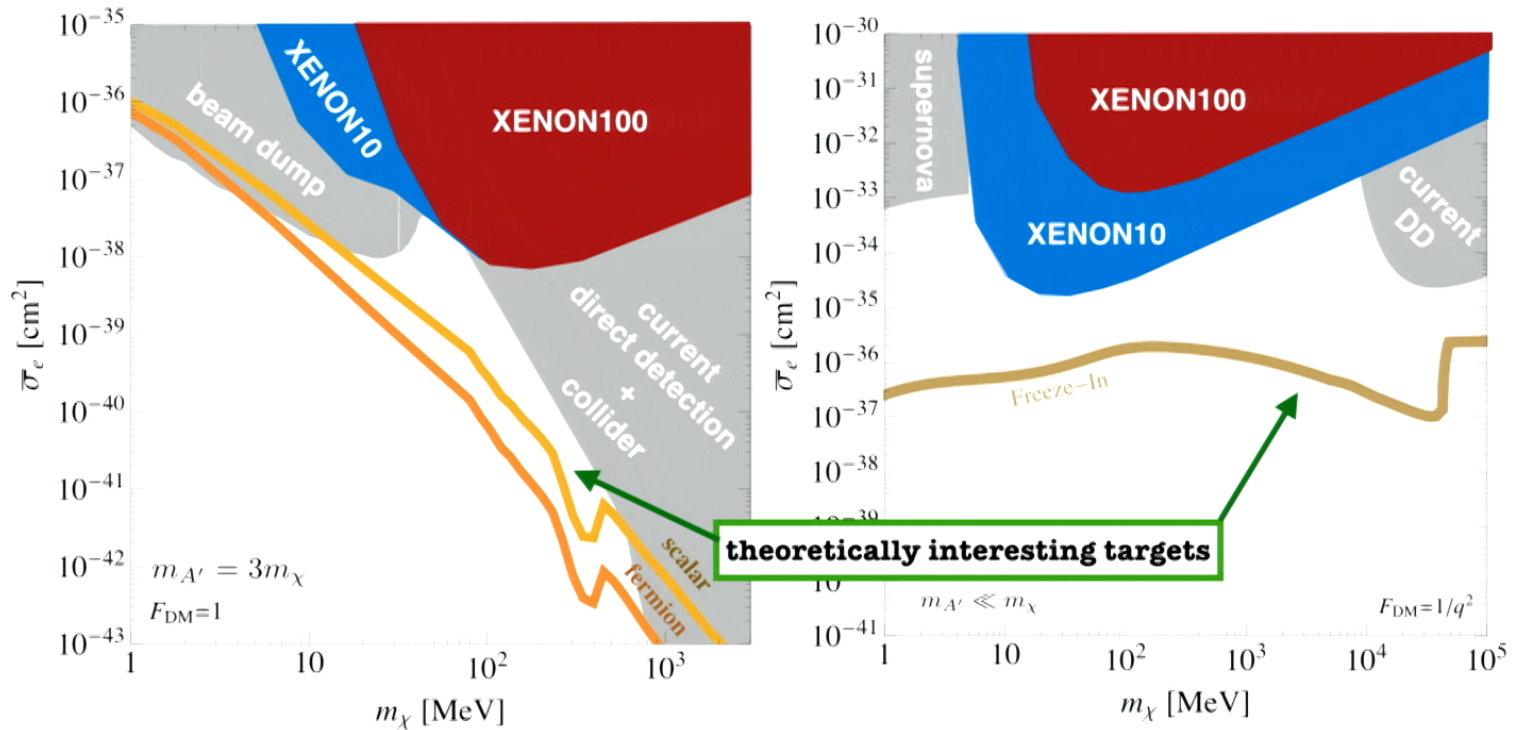


dark photon



Essig, Volansky, TTY [1703.00910]

dark photon



Essig, Volansky, TTY [1703.00910]

electron energy

- noble gases: $\Delta E_e \sim 10 \text{ eV}$
- semiconductors: $\Delta E_e \sim 1 \text{ eV}$

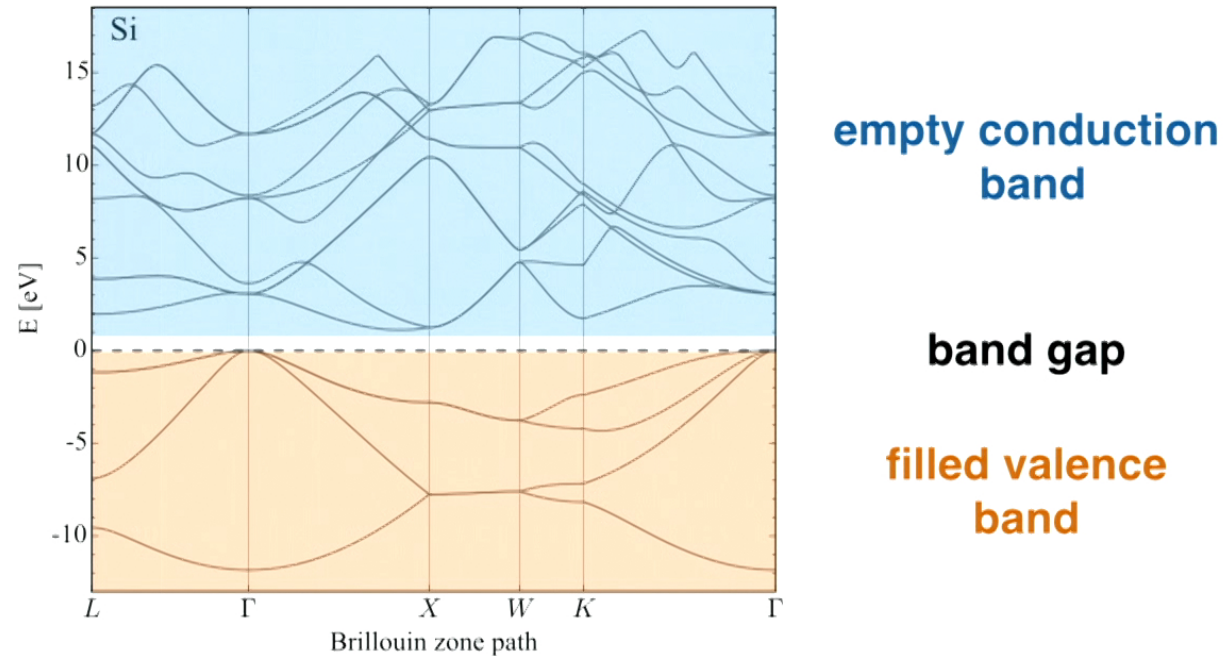
sets the limit in lower mass reach

number density

- xenon: 1.4×10^{22} atoms/cm³
- silicon: 5.0×10^{22} atoms/cm³

sets the limit in lower cross-section reach

Semiconductor targets



Essig, Fernandez-Serra, Mardon, Soto, TTY [1509.01598] JHEP 1605 (2016) 046

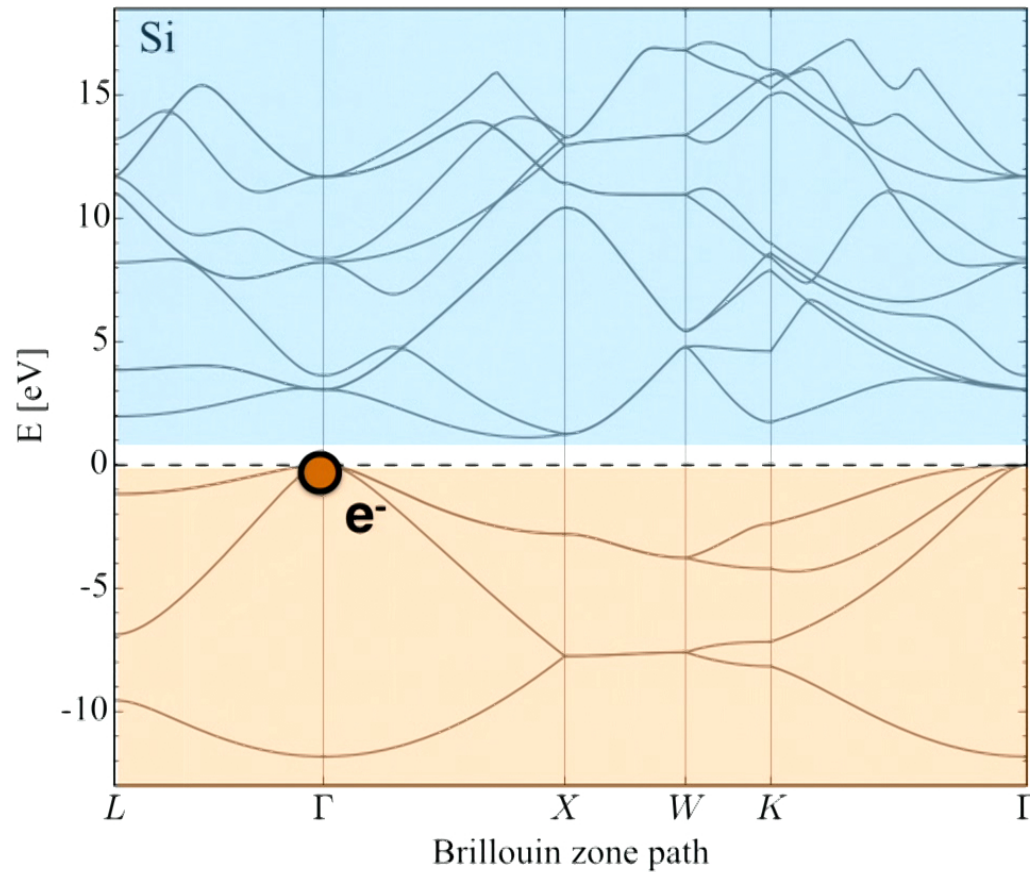
see also:

Essig, Mardon, Volansky [1108.5383] Phys.Rev. D85 (2012) 076007

Graham, Kaplan, Rajendran, Walters [1203.2531] Phys.Dark Univ. 1 (2012) 32-49

Lee, Lisanti, Mishra-Sharma, Safdi [1508.07361] Phys.Rev. D92 (2015) 083517

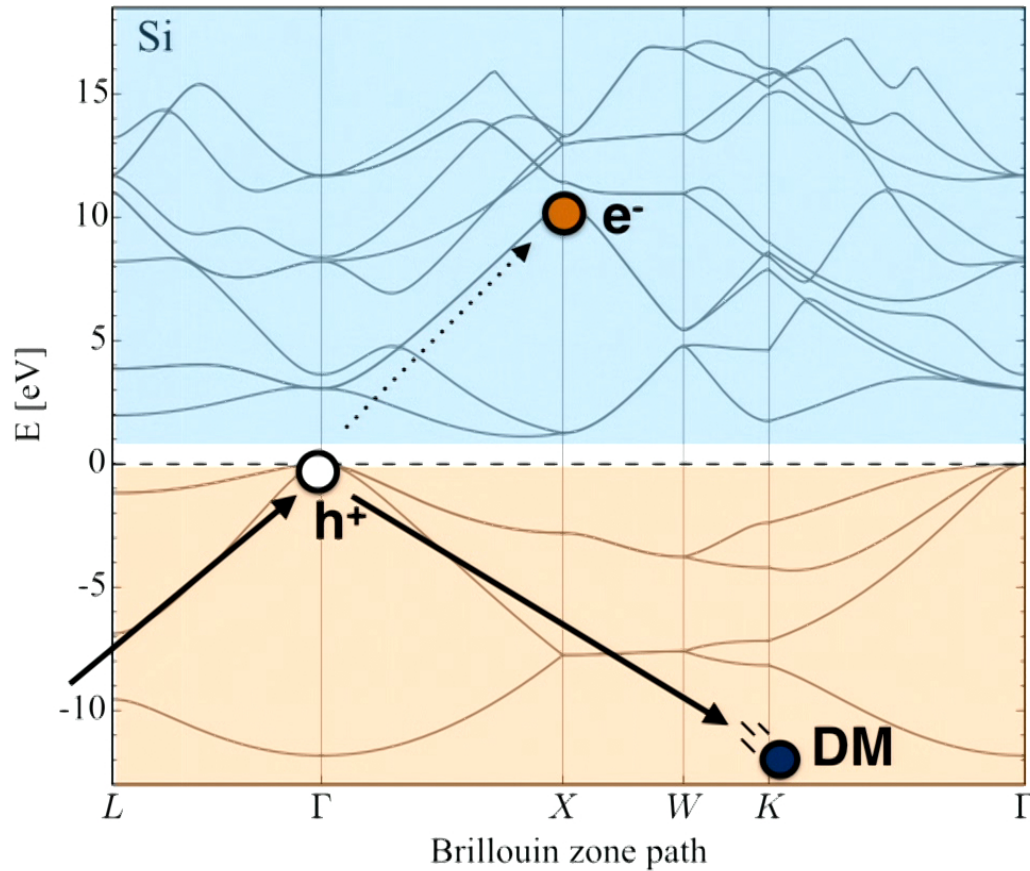
Semiconductor targets



band gap [eV]

Ge	0.67
Si	1.1
GaAs	1.5
NaI	5.9
CsI	6.4

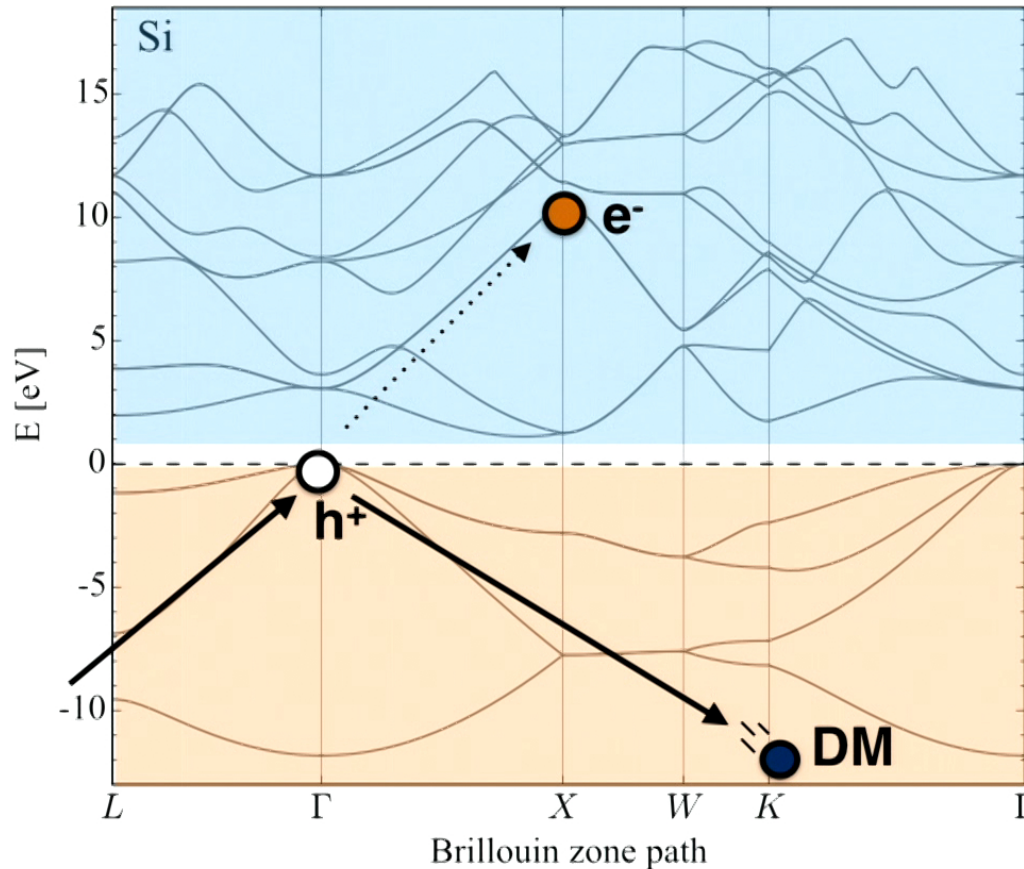
Semiconductor targets



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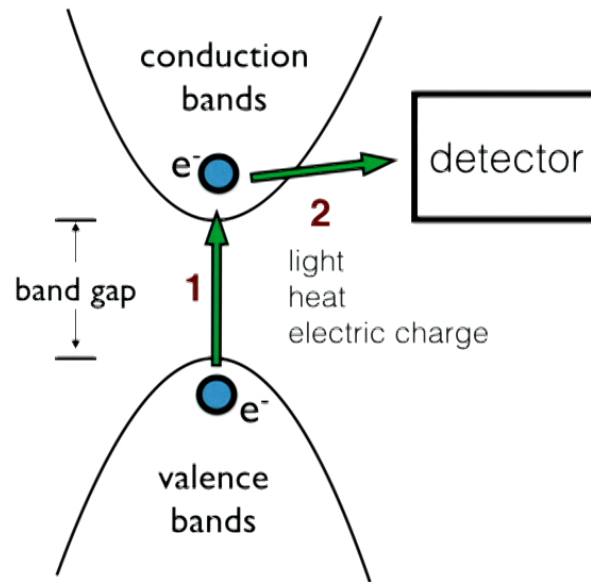
Semiconductor targets



apply an electric field and extract the electron(s) “ionization”

e^-/h^+ recombine to produce photon(s) “scintillation”

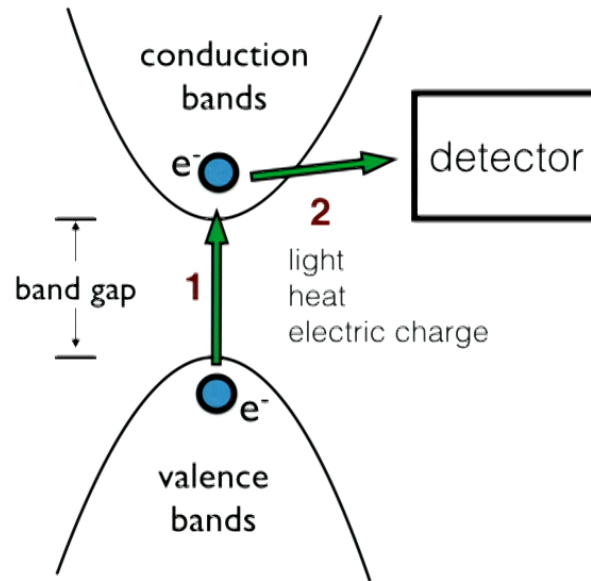
solid



$$\left| f_{i \rightarrow i'}(\vec{q}, \vec{k}) \right|^2 = \frac{V}{(2\pi)^3} \int_{\text{BZ}} d^3 k' \left| \int d^3 x \psi_{i', \vec{k}'}^*(\vec{x}) \psi_{i, \vec{k}}(\vec{x}) e^{i\vec{q} \cdot \vec{x}} \right|^2$$

electrons in a solid are part of a complicated, many-body system

solid



$$\left| f_{i \rightarrow i'}(\vec{q}, \vec{k}) \right|^2 = \frac{V}{(2\pi)^3} \int_{\text{BZ}} d^3 k' \left| \int d^3 x \psi_{i', \vec{k}'}^*(\vec{x}) \psi_{i, \vec{k}}(\vec{x}) e^{i\vec{q} \cdot \vec{x}} \right|^2$$

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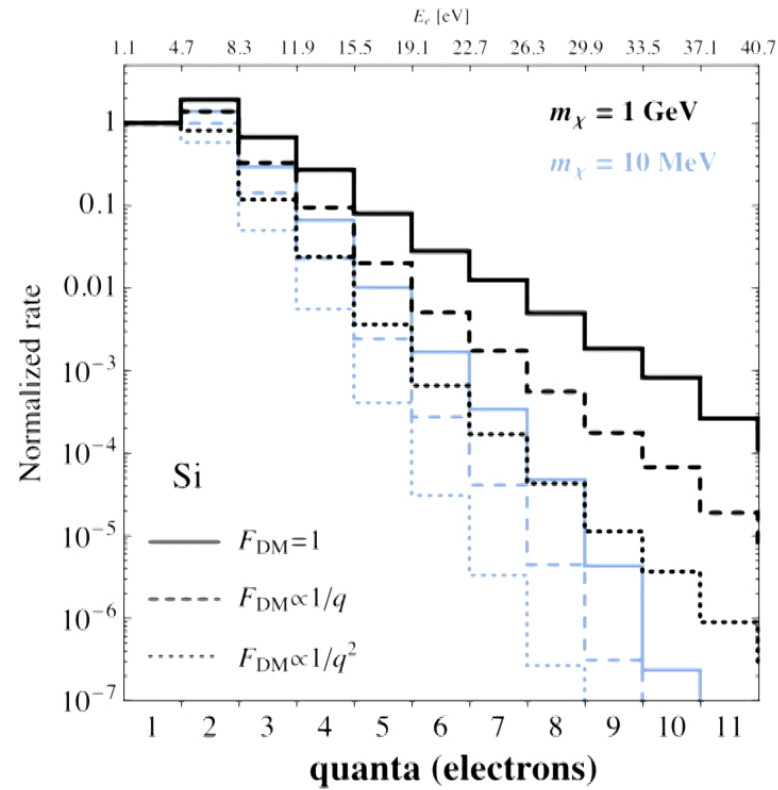
<http://www.quantum-espresso.org/>

- **open source code that calculates electronic structure within density functional theory (DFT) using plane waves and pseudopotentials**

- **module QEdark:**

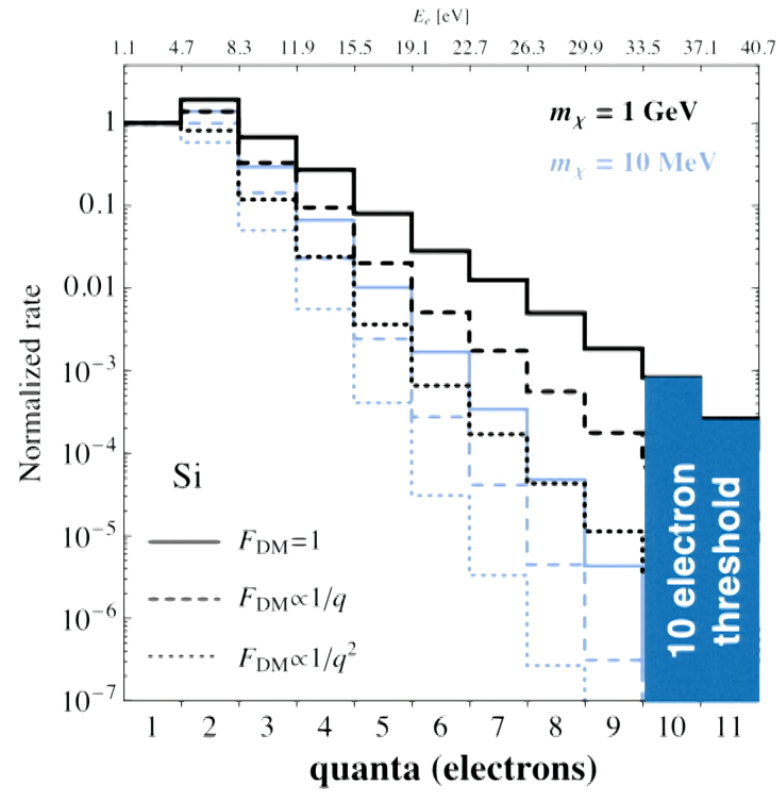
<http://ddldm.physics.sunysb.edu/>

silicon



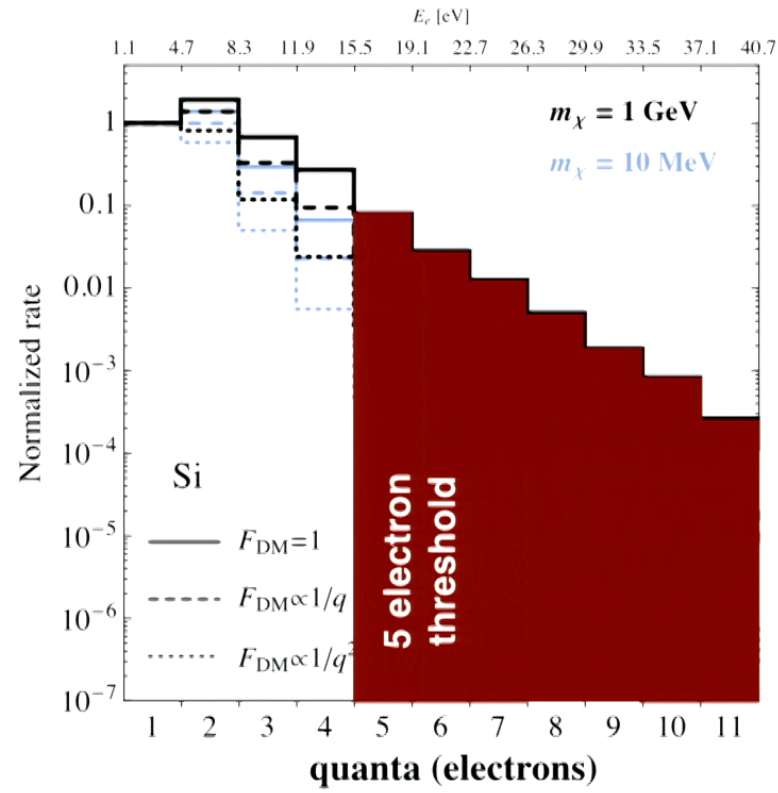
Essig, Fernandez-Serra, Mardon, Soto, TTY [1509.01598]

silicon



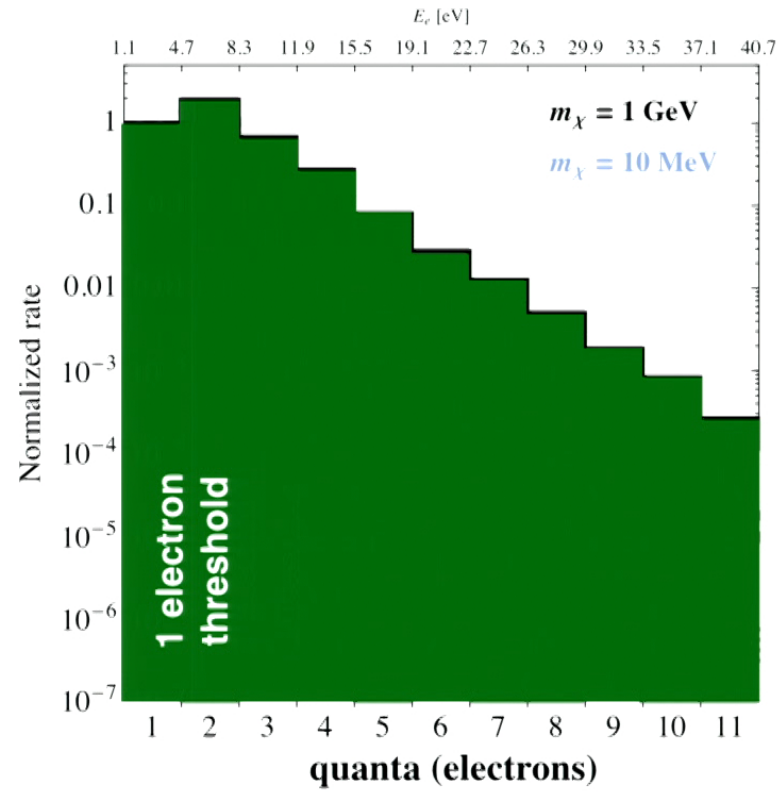
Essig, Fernandez-Serra, Mardon, Soto, TTY [1509.01598]

silicon



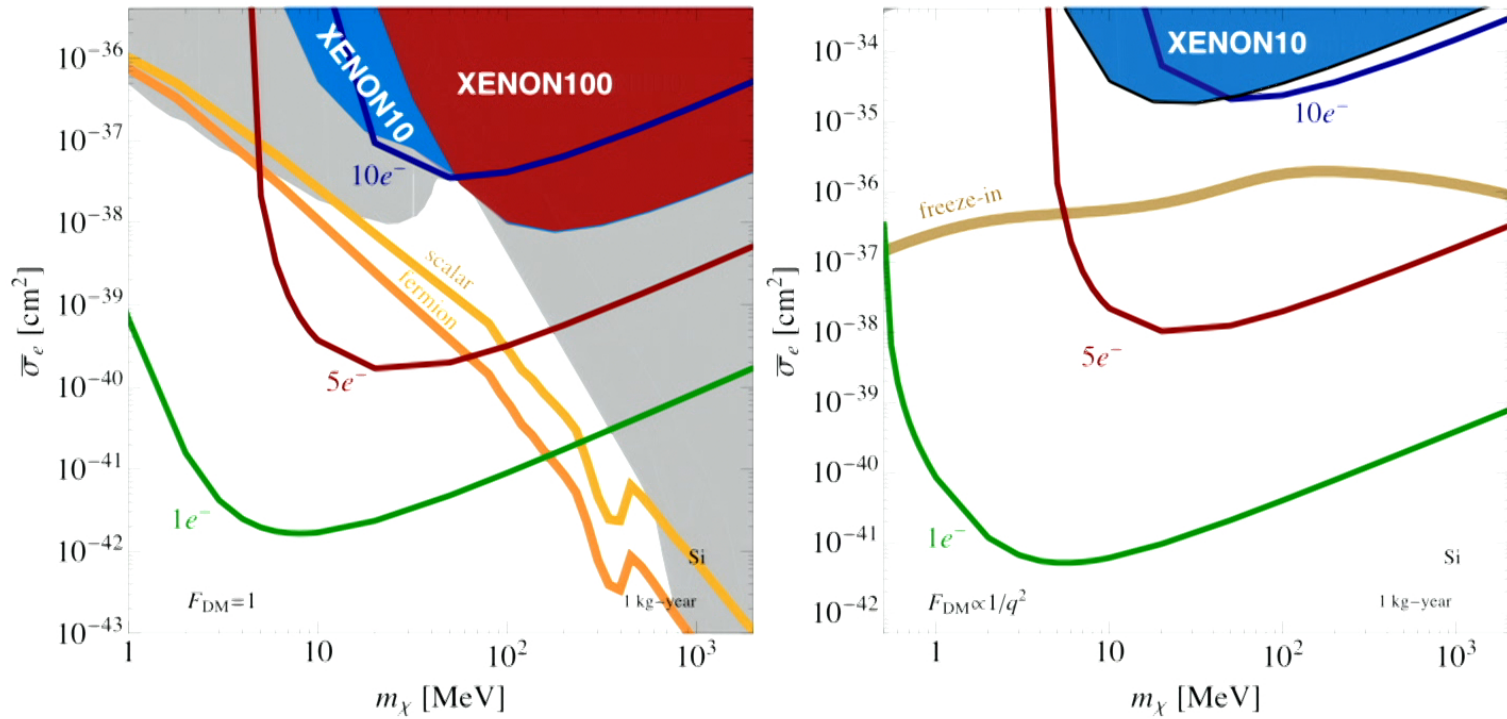
Essig, Fernandez-Serra, Mardon, Soto, TTY [1509.01598]

silicon



Essig, Fernandez-Serra, Mardon, Soto, TTY [1509.01598]

silicon



Essig, Fernandez-Serra, Mardon, Soto, TTY [1509.01598]

SENSEI

Sub-Electron-Noise Skipper CCD Experimental Instrument

CERN: **Tien-Tien Yu**

Fermilab: **Javier Tiffenberg, Yann Guardincerri, Miguel Sofo Haro**

LBNL: **Steve Holland, Christopher Bebek**

Stanford University*: **Jeremy Mardon**

Stony Brook: **Rouven Essig**

Tel Aviv University: **Tomer Volansky**

Experimentalists

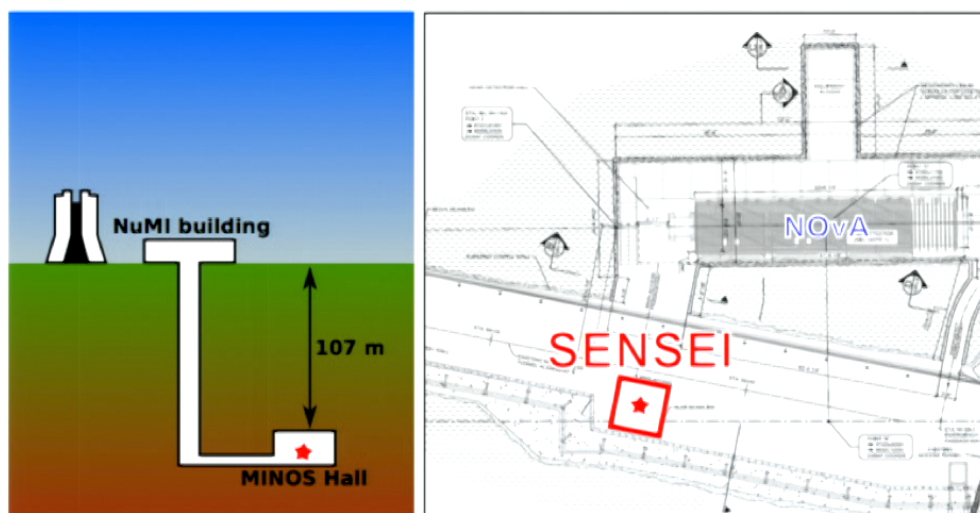
Theorists

SENSEI

Sub-Electron-Noise Skipper CCD Experimental Instrument

Whats next: Installation @MINOS & low radiation package

Technology demonstration: installation at shallow underground site



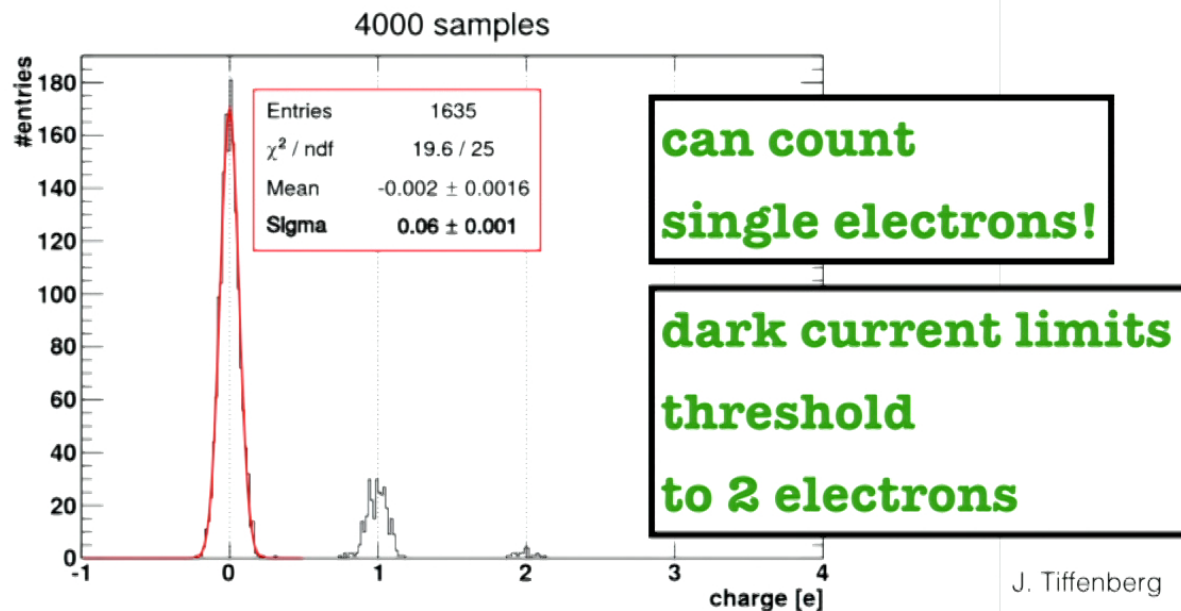
J. Tiffenberg



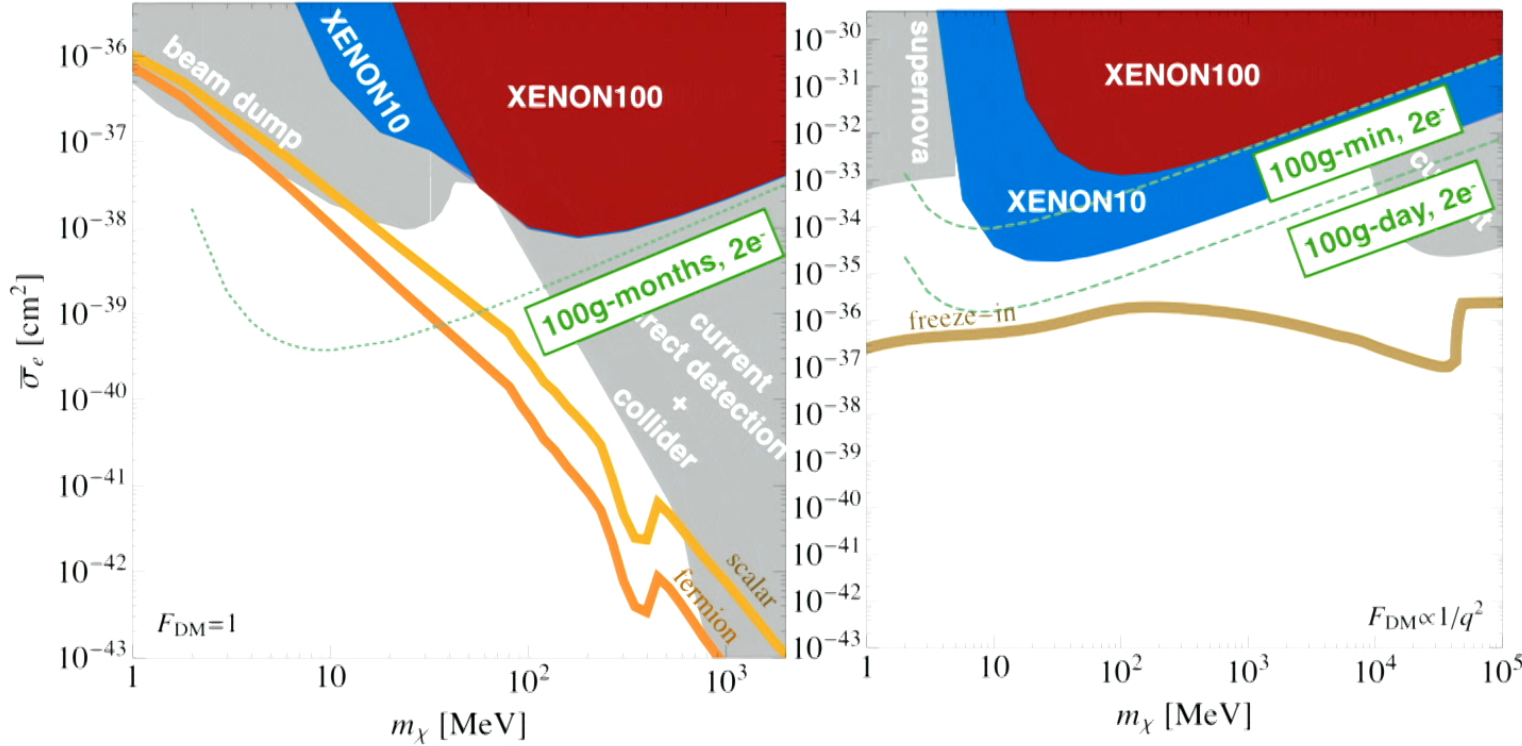
SENSEI

Sub-Electron-Noise Skipper CCD Experimental Instrument

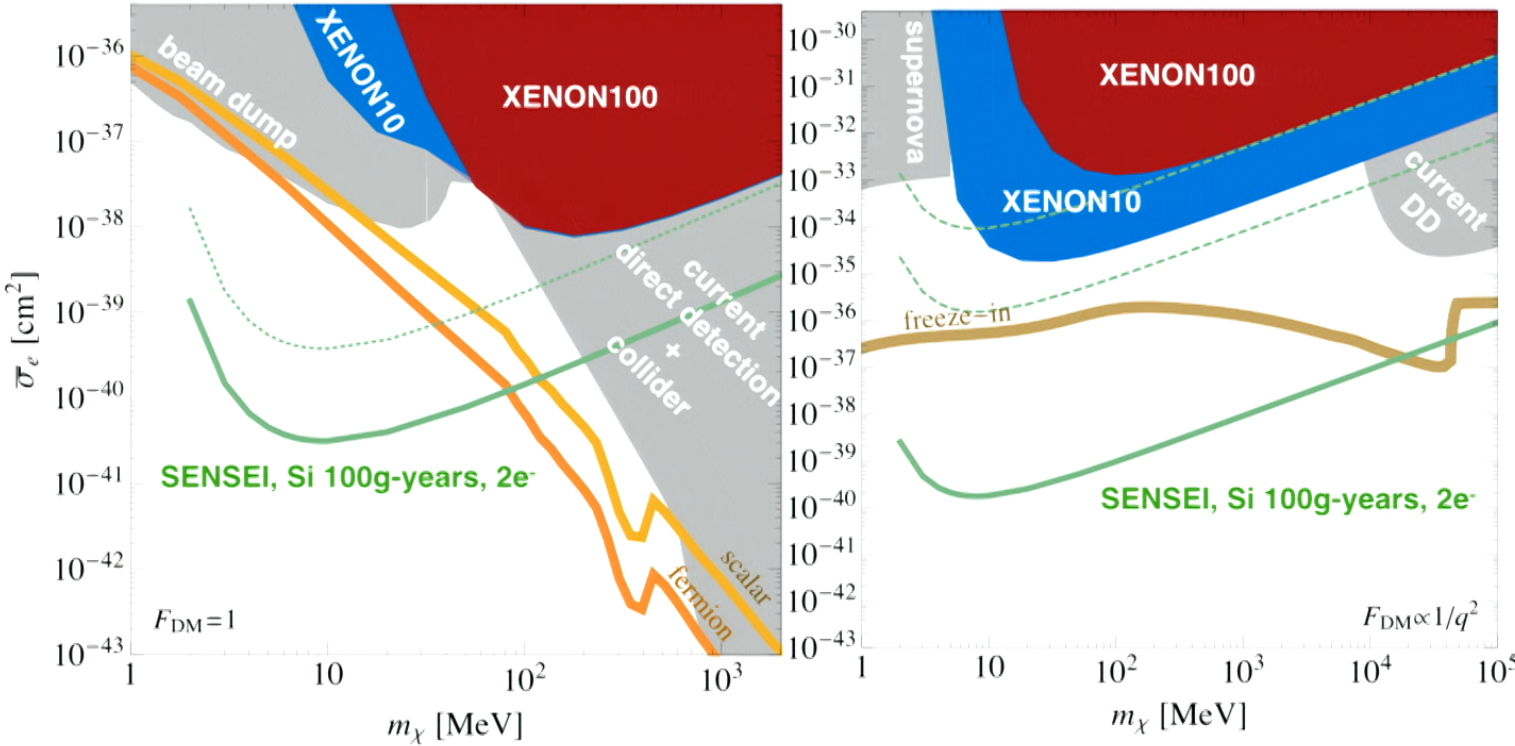
Charge in pixel distribution. Counting electrons: 0, 1, 2..



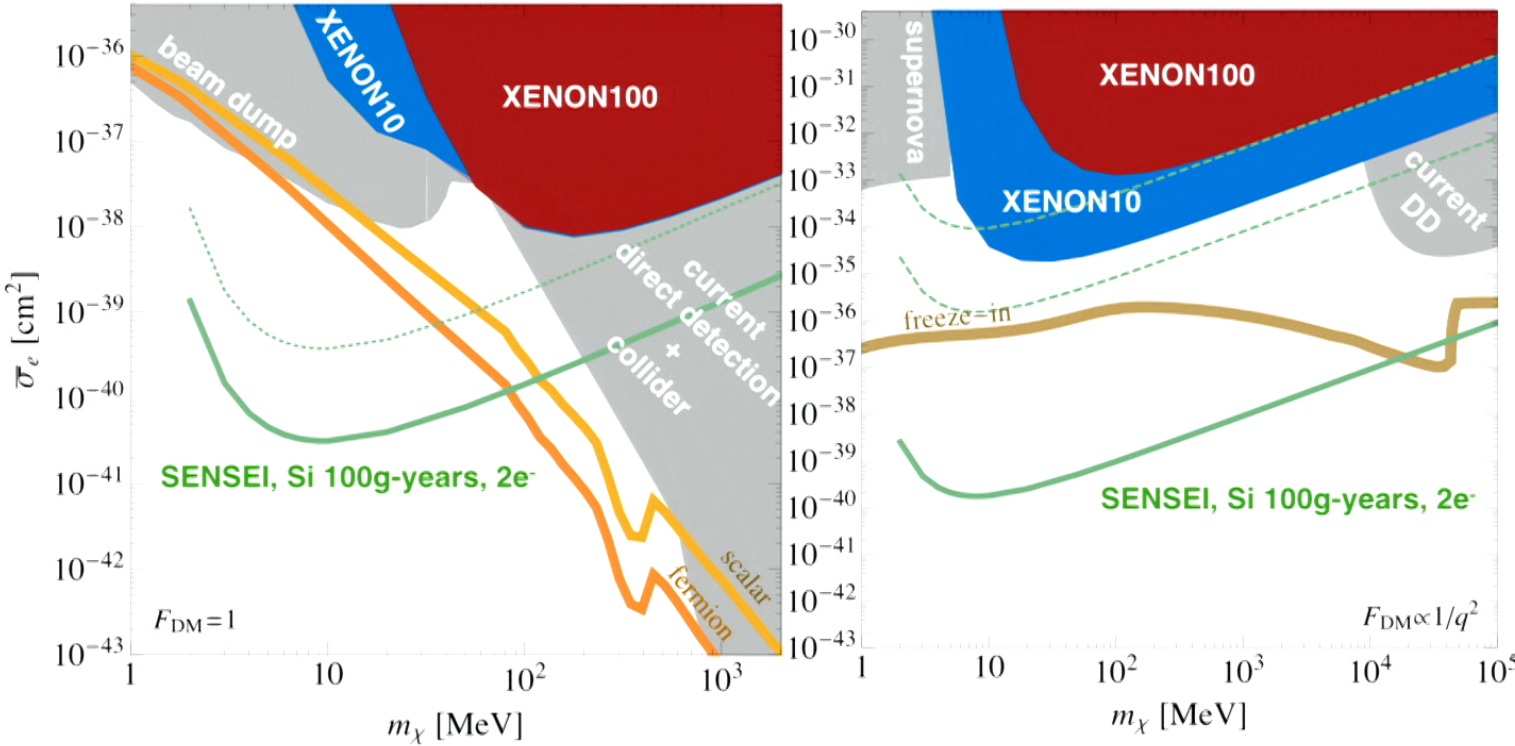
SENSEI



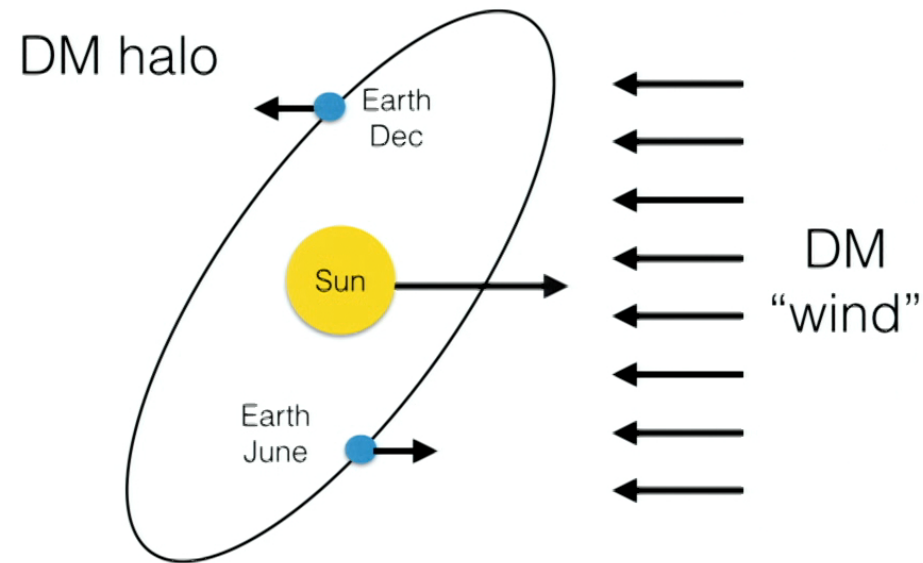
SENSEI



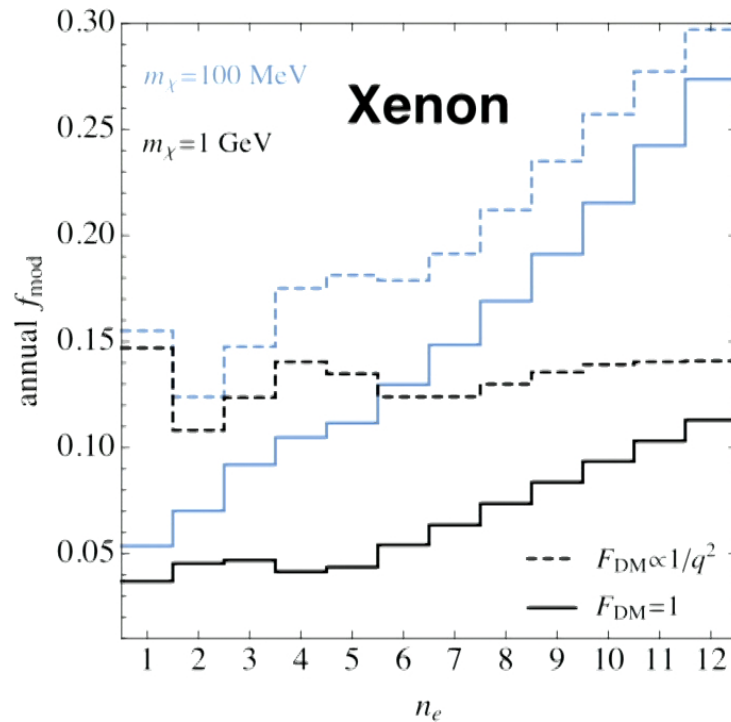
SENSEI



annual modulation



annual modulation



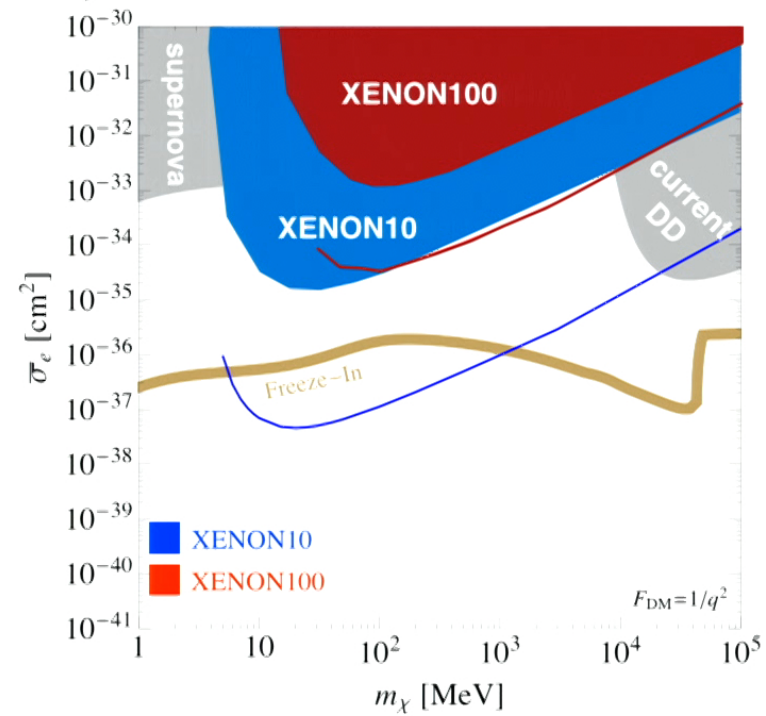
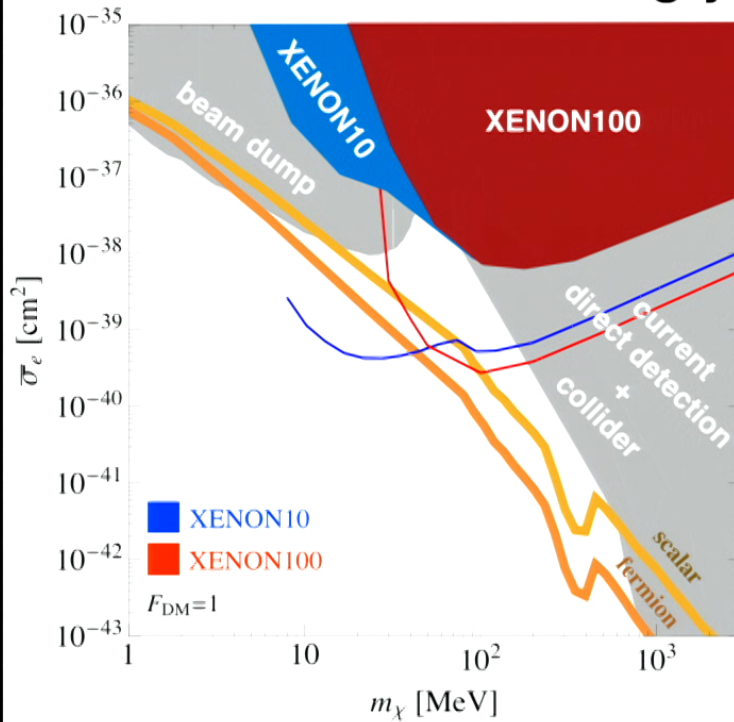
$$f_{\text{mod}} = \frac{R_{\text{max}} - R_{\text{min}}}{2R_{\text{mean}}}$$

$$\text{sig} = \frac{f_{\text{mod}} S}{\sqrt{S + B}}$$

$$\text{sig} = 1.645 = 90\% \text{ CL}$$

annual modulation

1000 kg-years, 90%CL



Essig, Volansky, TTY [1703.00910]

ingredients

solid state physics

$$\frac{d\langle\sigma v\rangle}{d\ln E_R} = \frac{\bar{\sigma}_e}{8\mu_{\chi e}^2} \int q dq |f(k, q)|^2 |F_{DM}(q)|^2 \eta(v_{min})$$

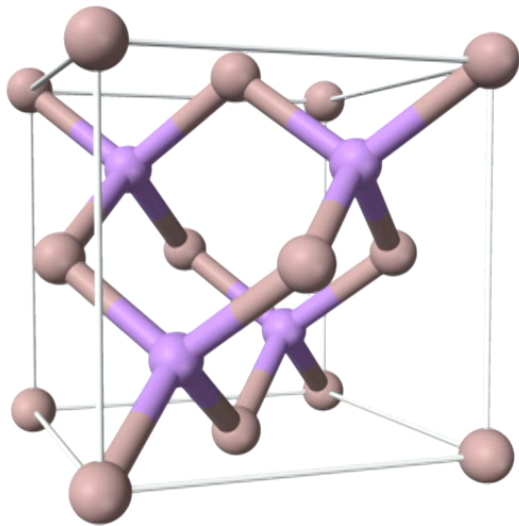


$$|f_{i\rightarrow i'}(\vec{q}, \vec{k})|^2 = \left| \sum_G \psi_{i'}^*(\vec{k} + \vec{G} + \vec{q}) \psi_i(\vec{k} + \vec{G}) \right|^2$$

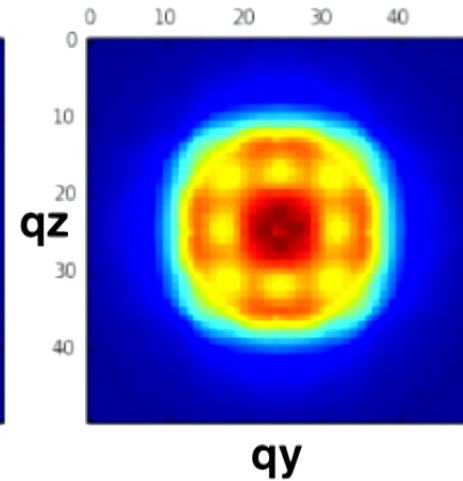
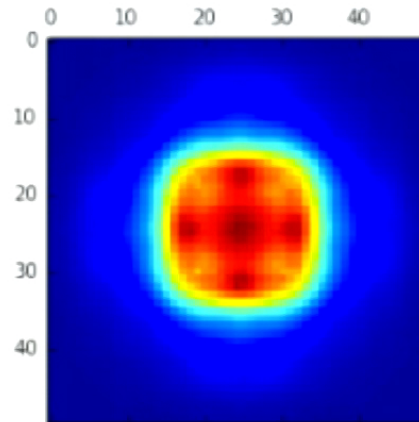
contains directional dependence
***potentially powerful signal discrimination!**

directionality

Gallium Arsenide (GaAs)



<https://en.wikipedia.org/wiki/File:Gallium-arsenide-unit-cell-3D-balls.png>

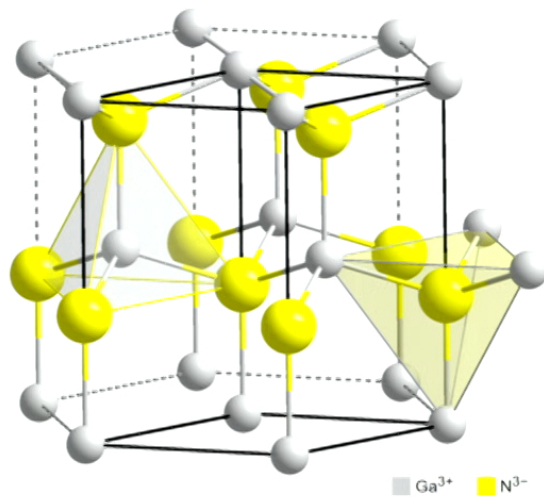


Essig, Mardon, Soto, Volansky, TTY (in preparation)

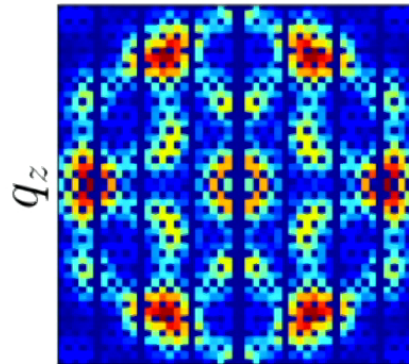
preliminary

directionality

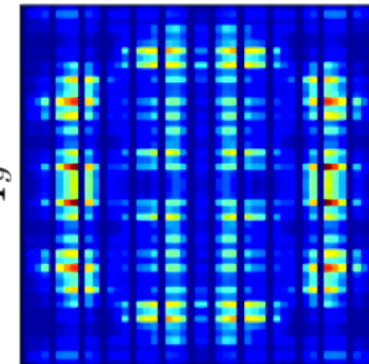
Gallium Nitride (GaN)



https://en.wikipedia.org/wiki/File:Wurtzite_polyhedra.png



y VS z

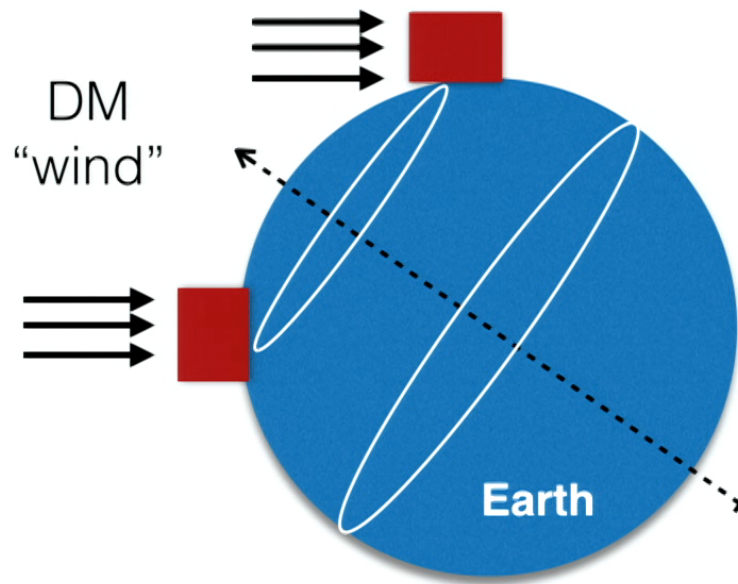


x VS y

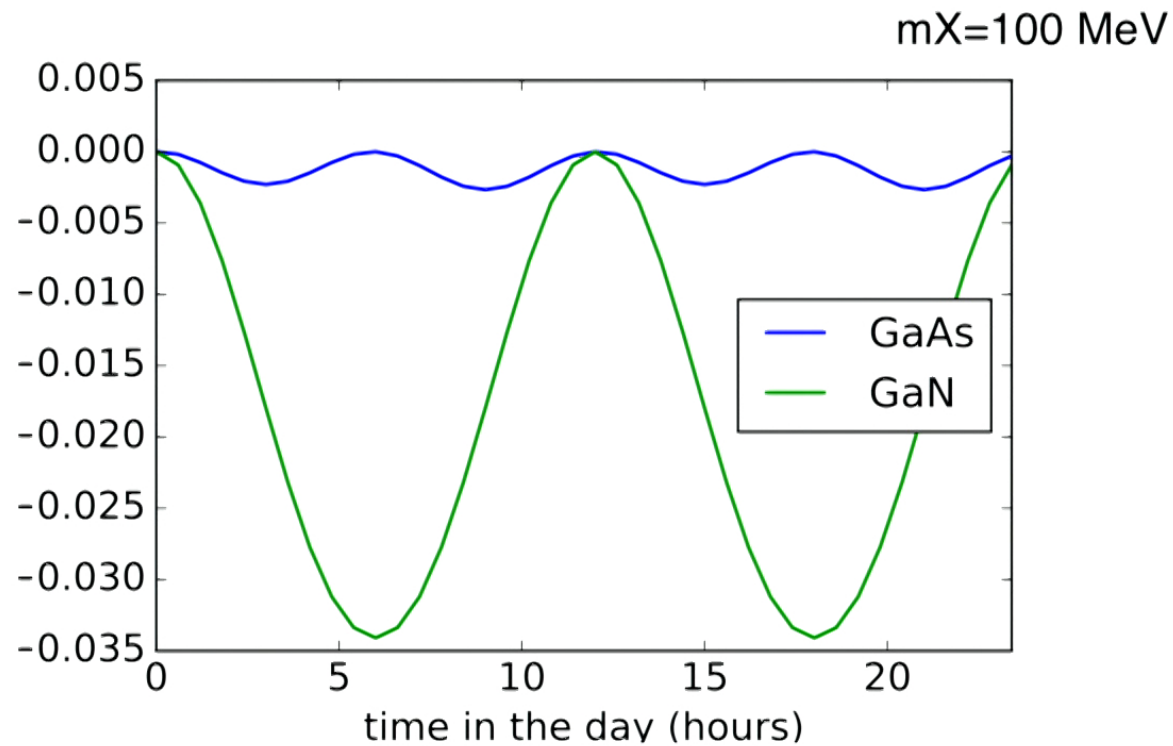
Essig, Mardon, Soto, Volansky, TTY (in preparation)

preliminary

directionality



directionality



Essig, Mardon, Soto, Volansky, TTY (in preparation)

preliminary

conclusions

- DM-electron scattering allows us to reach sub-GeV DM masses
- current constraints come from XENON10/XENON100 S2-only analyses
- near-future semiconductor targets like SENSEI will reach unprecedented sensitivity
- sensitivity to velocity tail means large modulation in rate
- rigid structure of crystal may allow for directional detection